1 Ordering Information

Table 1.1 (p. 2) shows the available EFM32G200 devices.

Table 1.1. Ordering Information

Ordering Code	Flash (kB)	RAM (kB)	Max Speed (MHz)	Supply Voltage (V)	Temperature (ºC)	Package
EFM32G200F16-QFN32	16	8	32	1.98 - 3.8	-40 - 85	QFN32
EFM32G200F32-QFN32	32	8	32	1.98 - 3.8	-40 - 85	QFN32
EFM32G200F64-QFN32	64	16	32	1.98 - 3.8	-40 - 85	QFN32

Adding the suffix 'T' to the part number (e.g. EFM32G200F16-QFN32T) denotes tray.

Visit **www.silabs.com** for information on global distributors and representatives.

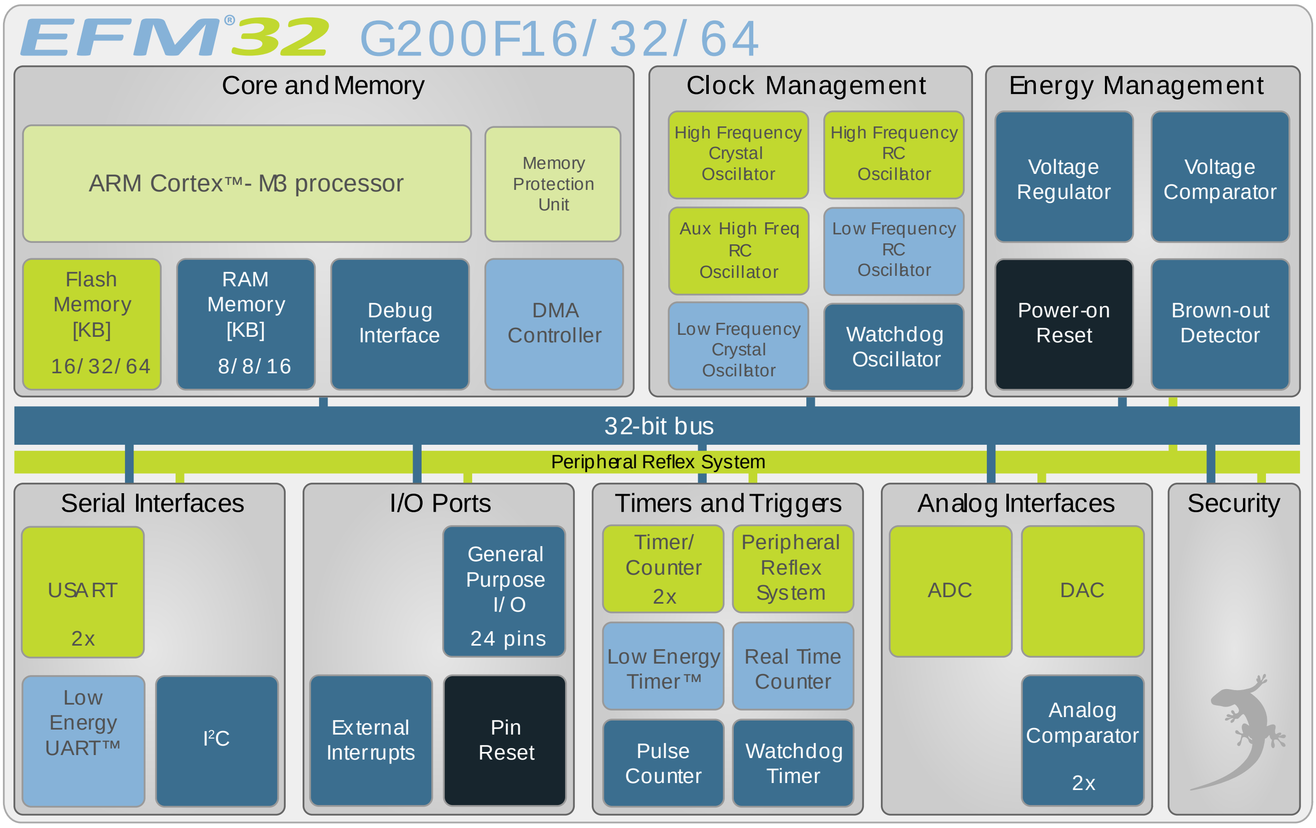
2 System Summary

2.1 System Introduction

The EFM32 MCUs are the world's most energy friendly microcontrollers. With a unique combination of the powerful 32-bit ARM Cortex-M3, innovative low energy techniques, short wake-up time from energy saving modes, and a wide selection of peripherals, the EFM32G microcontroller is well suited for any battery operated application as well as other systems requiring high performance and low-energy consumption. This section gives a short introduction to each of the modules in general terms and also shows a summary of the configuration for the EFM32G200 devices. For a complete feature set and in-depth information on the modules, the reader is referred to the *EFM32G Reference Manual*.

A block diagram of the EFM32G200 is shown in Figure 2.1 (p. 3) .

Figure 2.1. Block Diagram



2.1.1 ARM Cortex-M3 Core

The ARM Cortex-M3 includes a 32-bit RISC processor which can achieve as much as 1.25 Dhrystone MIPS/MHz. A Memory Protection Unit with support for up to 8 memory segments is included, as well as a Wake-up Interrupt Controller handling interrupts triggered while the CPU is asleep. The EFM32 implementation of the Cortex-M3 is described in detail in *EFM32G Cortex-M3 Reference Manual*.

2.1.2 Debug Interface (DBG)

This device includes hardware debug support through a 2-pin serial-wire debug interface . In addition there is also a 1-wire Serial Wire Viewer pin which can be used to output profiling information, data trace and software-generated messages.

2.1.3 Memory System Controller (MSC)

The Memory System Controller (MSC) is the program memory unit of the EFM32G microcontroller. The flash memory is readable and writable from both the Cortex-M3 and DMA. The flash memory is divided into two blocks; the main block and the information block. Program code is normally written to the main block. Additionally, the information block is available for special user data and flash lock bits. There is also a read-only page in the information block containing system and device calibration data. Read and write operations are supported in the energy modes EM0 and EM1.

2.1.4 Direct Memory Access Controller (DMA)

The Direct Memory Access (DMA) controller performs memory operations independently of the CPU. This has the benefit of reducing the energy consumption and the workload of the CPU, and enables the system to stay in low energy modes when moving for instance data from the USART to RAM or from the External Bus Interface to a PWM-generating timer. The DMA controller uses the PL230 µDMA controller licensed from ARM.

2.1.5 Reset Management Unit (RMU)

The RMU is responsible for handling the reset functionality of the EFM32G.

2.1.6 Energy Management Unit (EMU)

The Energy Management Unit (EMU) manage all the low energy modes (EM) in EFM32G microcontrollers. Each energy mode manages if the CPU and the various peripherals are available. The EMU can also be used to turn off the power to unused SRAM blocks.

2.1.7 Clock Management Unit (CMU)

The Clock Management Unit (CMU) is responsible for controlling the oscillators and clocks on-board the EFM32G. The CMU provides the capability to turn on and off the clock on an individual basis to all peripheral modules in addition to enable/disable and configure the available oscillators. The high degree of flexibility enables software to minimize energy consumption in any specific application by not wasting power on peripherals and oscillators that are inactive.

2.1.8 Watchdog (WDOG)

The purpose of the watchdog timer is to generate a reset in case of a system failure, to increase application reliability. The failure may e.g. be caused by an external event, such as an ESD pulse, or by a software failure.

2.1.9 Peripheral Reflex System (PRS)

The Peripheral Reflex System (PRS) system is a network which lets the different peripheral module communicate directly with each other without involving the CPU. Peripheral modules which send out Reflex signals are called producers. The PRS routes these reflex signals to consumer peripherals which apply actions depending on the data received. The format for the Reflex signals is not given, but edge triggers and other functionality can be applied by the PRS.

2.1.10 Inter-Integrated Circuit Interface (I2C)

The I^2C module provides an interface between the MCU and a serial I^2C-bus. It is capable of acting as both a master and a slave, and supports multi-master buses. Both standard-mode, fast-mode and fast-mode plus speeds are supported, allowing transmission rates all the way from 10 kbit/s up to 1 Mbit/s. Slave arbitration and timeouts are also provided to allow implementation of an SMBus compliant system. The interface provided to software by the I^2C module, allows both fine-grained control of the transmission process and close to automatic transfers. Automatic recognition of slave addresses is provided in all energy modes.

2.1.11 Universal Synchronous/Asynchronous Receiver/Transmitter (USART)

The Universal Synchronous Asynchronous serial Receiver and Transmitter (USART) is a very flexible serial I/O module. It supports full duplex asynchronous UART communication as well as RS-485, SPI, MicroWire and 3-wire. It can also interface with ISO7816 SmartCards, and IrDA devices.

2.1.12 Pre-Programmed UART Bootloader

The bootloader presented in application note AN0003 is pre-programmed in the device at factory. Autobaud and destructive write are supported. The autobaud feature, interface and commands are described further in the application note.

2.1.13 Low Energy Universal Asynchronous Receiver/Transmitter (LEUART)

The unique LEUART^{TM}, the Low Energy UART, is a UART that allows two-way UART communication on a strict power budget. Only a 32.768 kHz clock is needed to allow UART communication up to 9600 baud/s. The LEUART includes all necessary hardware support to make asynchronous serial communication possible with minimum of software intervention and energy consumption.

2.1.14 Timer/Counter (TIMER)

The 16-bit general purpose Timer has 3 compare/capture channels for input capture and compare/Pulse-Width Modulation (PWM) output. TIMER0 also includes a Dead-Time Insertion module suitable for motor control applications.

2.1.15 Real Time Counter (RTC)

The Real Time Counter (RTC) contains a 24-bit counter and is clocked either by a 32.768 kHz crystal oscillator, or a 32.768 kHz RC oscillator. In addition to energy modes EM0 and EM1, the RTC is also available in EM2. This makes it ideal for keeping track of time since the RTC is enabled in EM2 where most of the device is powered down.

2.1.16 Low Energy Timer (LETIMER)

The unique LETIMER^{TM}, the Low Energy Timer, is a 16-bit timer that is available in energy mode EM2 in addition to EM1 and EM0. Because of this, it can be used for timing and output generation when most of the device is powered down, allowing simple tasks to be performed while the power consumption of the system is kept at an absolute minimum. The LETIMER can be used to output a variety of waveforms with minimal software intervention. It is also connected to the Real Time Counter (RTC), and can be configured to start counting on compare matches from the RTC.

2.1.17 Pulse Counter (PCNT)

The Pulse Counter (PCNT) can be used for counting pulses on a single input or to decode quadrature encoded inputs. It runs off either the internal LFACLK or the PCNTn_S0IN pin as external clock source. The module may operate in energy mode EM0 - EM3.

2.1.18 Analog Comparator (ACMP)

The Analog Comparator is used to compare the voltage of two analog inputs, with a digital output indicating which input voltage is higher. Inputs can either be one of the selectable internal references or from external pins. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.19 Voltage Comparator (VCMP)

The Voltage Supply Comparator is used to monitor the supply voltage from software. An interrupt can be generated when the supply falls below or rises above a programmable threshold. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

2.1.20 Analog to Digital Converter (ADC)

The ADC is a Successive Approximation Register (SAR) architecture, with a resolution of up to 12 bits at up to one million samples per second. The integrated input mux can select inputs from 4 external pins and 6 internal signals.

2.1.21 Digital to Analog Converter (DAC)

The Digital to Analog Converter (DAC) can convert a digital value to an analog output voltage. The DAC is fully differential rail-to-rail, with 12-bit resolution. It has one single ended output buffer connected to channel 0. The DAC may be used for a number of different applications such as sensor interfaces or sound output.

2.1.22 General Purpose Input/Output (GPIO)

In the EFM32G200, there are 24 General Purpose Input/Output (GPIO) pins, which are divided into ports with up to 16 pins each. These pins can individually be configured as either an output or input. More advanced configurations like open-drain, filtering and drive strength can also be configured individually for the pins. The GPIO pins can also be overridden by peripheral pin connections, like Timer PWM outputs or USART communication, which can be routed to several locations on the device. The GPIO supports up to 14 asynchronous external pin interrupts, which enables interrupts from any pin on the device. Also, the input value of a pin can be routed through the Peripheral Reflex System to other peripherals.

2.2 Configuration Summary

The features of the EFM32G200 is a subset of the feature set described in the EFM32G Reference Manual. Table 2.1 (p. 6) describes device specific implementation of the features.

Table 2.1. Configuration Summary

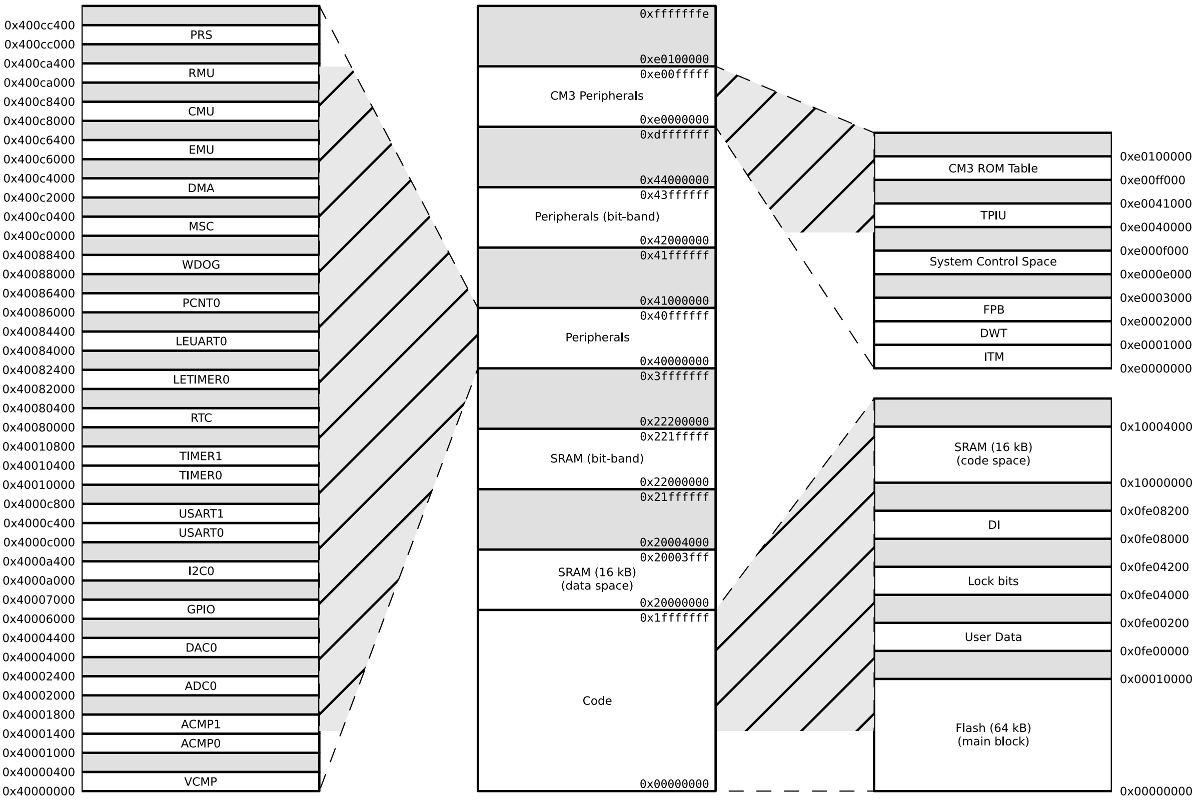
Module	Configuration	Pin Connections
Cortex-M3	Full configuration	NA
DBG	Full configuration	DBG_SWCLK, DBG_SWDIO, DBG_SWO
MSC	Full configuration	NA
DMA	Full configuration	NA
RMU	Full configuration	NA
EMU	Full configuration	NA
CMU	Full configuration	CMU_OUT0, CMU_OUT1
WDOG	Full configuration	NA
PRS	Full configuration	NA
I2C0	Full configuration	I2C0_SDA, I2C0_SCL
USART0	Full configuration with IrDA	US0_TX, US0_RX. US0_CLK, US0_CS
USART1	Full configuration	US1_TX, US1_RX, US1_CLK, US1_CS

Module	Configuration	Pin Connections
LEUART0	Full configuration	LEU0_TX, LEU0_RX
TIMER0	Full configuration with DTI	TIM0_CC[2:0], TIM0_CDTI[2:0]
TIMER1	Full configuration	TIM1_CC[2:0]
RTC	Full configuration	NA
LETIMER0	Full configuration	LET0_O[1:0]
PCNT0	Full configuration, 8-bit count register	PCNT0_S[1:0]
ACMP0	Full configuration	ACMP0_CH[1:0], ACMP0_O
ACMP1	Full configuration	ACMP1_CH[7:5], ACMP1_O
VCMP	Full configuration	NA
ADC0	Full configuration	ADC0_CH[7:4]
DAC0	Full configuration	DAC0_OUT[0]
GPIO	24 pins	Available pins are shown in Table 4.3 (p. 50)

2.3 Memory Map

The *EFM32G200* memory map is shown in Figure 2.2 (p. 7), with RAM and Flash sizes for the largest memory configuration.

Figure 2.2. EFM32G200 Memory Map with largest RAM and Flash sizes



3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on T_{AMB}=25°C and V_{DD}=3.0 V, as defined in Table 3.2 (p. 8), by simulation and/or technology characterisation unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 8), by simulation and/or technology characterisation unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 8) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 8) .

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Typ	Max	Unit
T_{STG}	Storage temperature range		-40		150[1]	°C
T_S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	°C
V_{DDMAX}	External main supply voltage		0		3.8	V
V_{IOPIN}	Voltage on any I/O pin		-0.3		V_{DD}+0.3	V
I_{IOMAX}	Current per I/O pin (sink)				100	mA
	Current per I/O pin (source)				-100	mA

[1] Based on programmed devices tested for 10000 hours at 150°C. Storage temperature affects retention of preprogrammed calibration values stored in flash. Please refer to the Flash section in the Electrical Characteristics for information on flash data retention for different temperatures.

3.3 General Operating Conditions

3.3.1 General Operating Conditions

Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Typ	Max	Unit
T_{AMB}	Ambient temperature range	-40		85	°C
V_{DDOP}	Operating supply voltage	1.98		3.8	V
f_{APB}	Internal APB clock frequency			32	MHz
f_{AHB}	Internal AHB clock frequency			32	MHz

3.4 Current Consumption

Table 3.3. Current Consumption

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{EM0}	EM0 current. No prescaling. Running prime number calculation code from Flash. (Production test condition = 14 MHz)	32 MHz HFXO, all peripheral clocks disabled, V_{DD}= 3.0 V		180		µA/ MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		181	206	µA/ MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		183	207	µA/ MHz
		14 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		185	211	µA/ MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		186	215	µA/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		191	218	µA/ MHz
		1.2 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		220		µA/ MHz
I_{EM1}	EM1 current (Production test condition = 14 MHz)	32 MHz HFXO, all peripheral clocks disabled, V_{DD}= 3.0 V		45		µA/ MHz
		28 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		47	62	µA/ MHz
		21 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		48	64	µA/ MHz
		14 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		50	69	µA/ MHz
		11 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		51	72	µA/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, V_{DD}= 3.0 V		56	83	µA/ MHz
		1.2 MHz HFRCO. all peripheral clocks disabled, V_{DD}= 3.0 V		103		µA/ MHz
I_{EM2}	EM2 current	EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V_{DD}= 3.0 V, T_{AMB}=25°C		0.9	1.5	µA
		EM2 current with RTC prescaled to 1 Hz, 32.768 kHz LFRCO, V_{DD}= 3.0 V, T_{AMB}=85°C		3.0	6.0	µA
I_{EM3}	EM3 current	V_{DD}= 3.0 V, T_{AMB}=25°C		0.59	1.0	µA
		V_{DD}= 3.0 V, T_{AMB}=85°C		2.75	5.8	µA
I_{EM4}	EM4 current	V_{DD}= 3.0 V, T_{AMB}=25°C		0.02	0.045	µA
		V_{DD}= 3.0 V, T_{AMB}=85°C		0.25	0.7	µA

3.4.1 EM0 Current Consumption

Figure 3.1. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 28 MHz

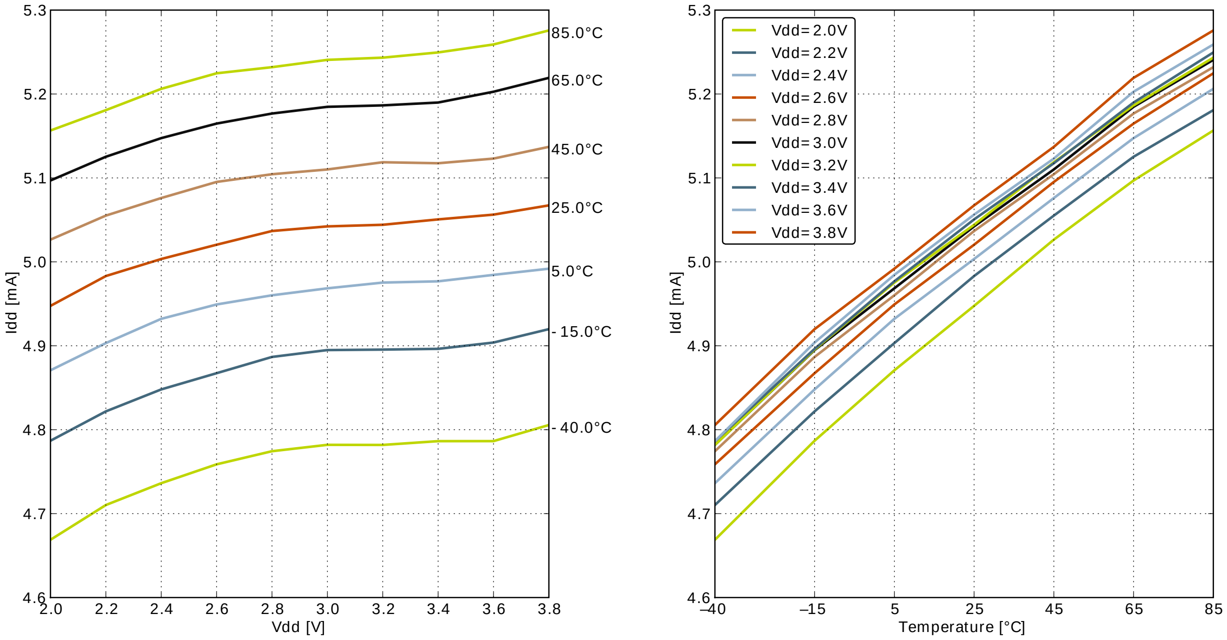


Figure 3.2. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 21 MHz

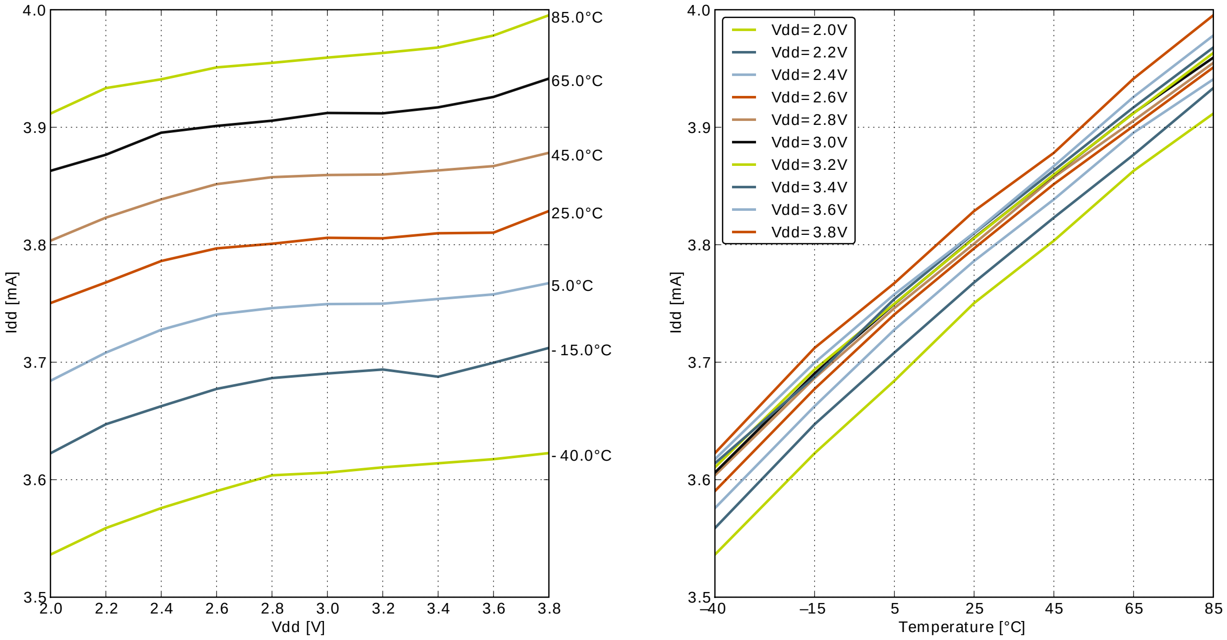


Figure 3.3. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 14 MHz

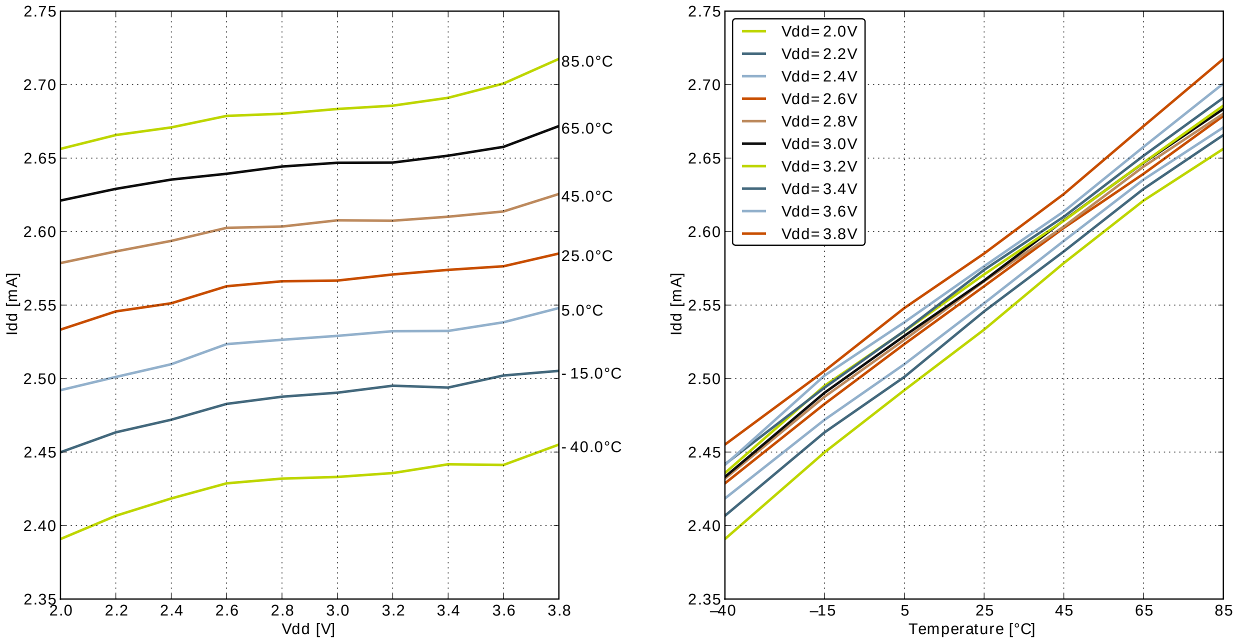


Figure 3.4. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 11 MHz

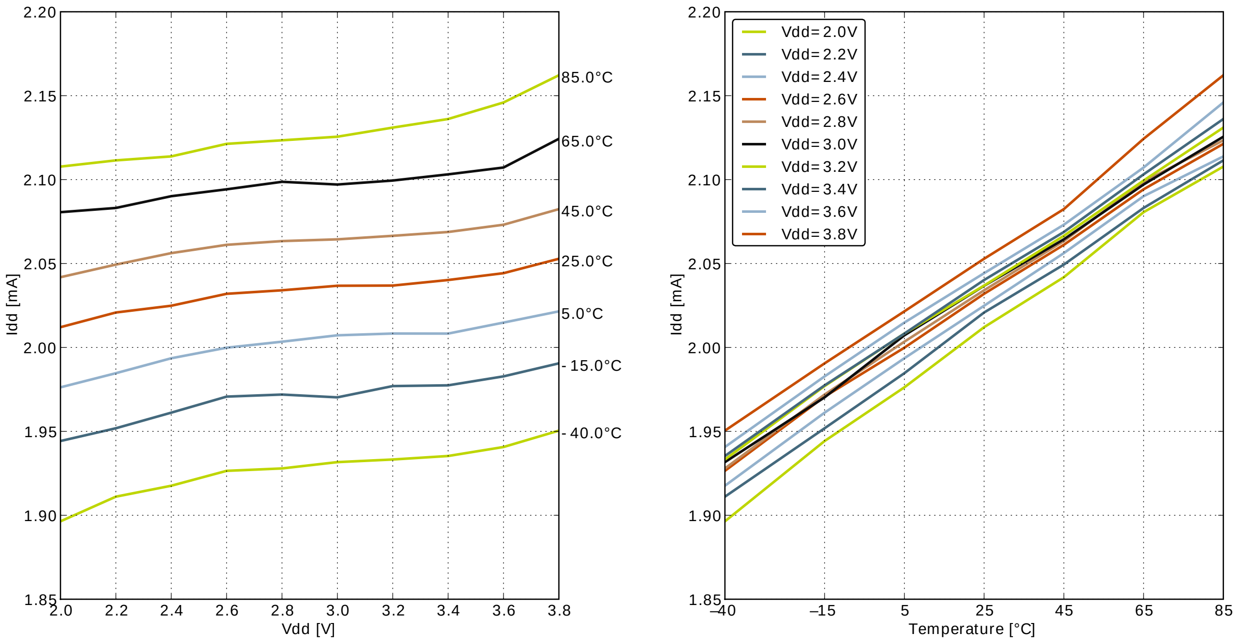
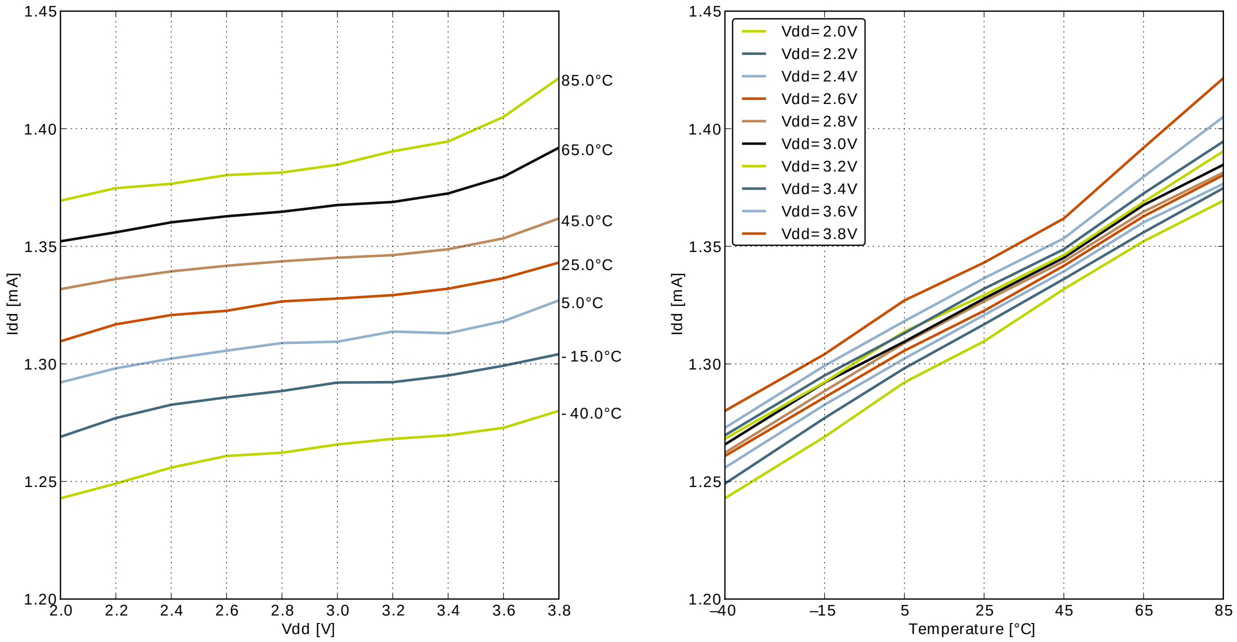


Figure 3.5. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 7 MHz



3.4.2 EM1 Current Consumption

Figure 3.6. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 28 MHz

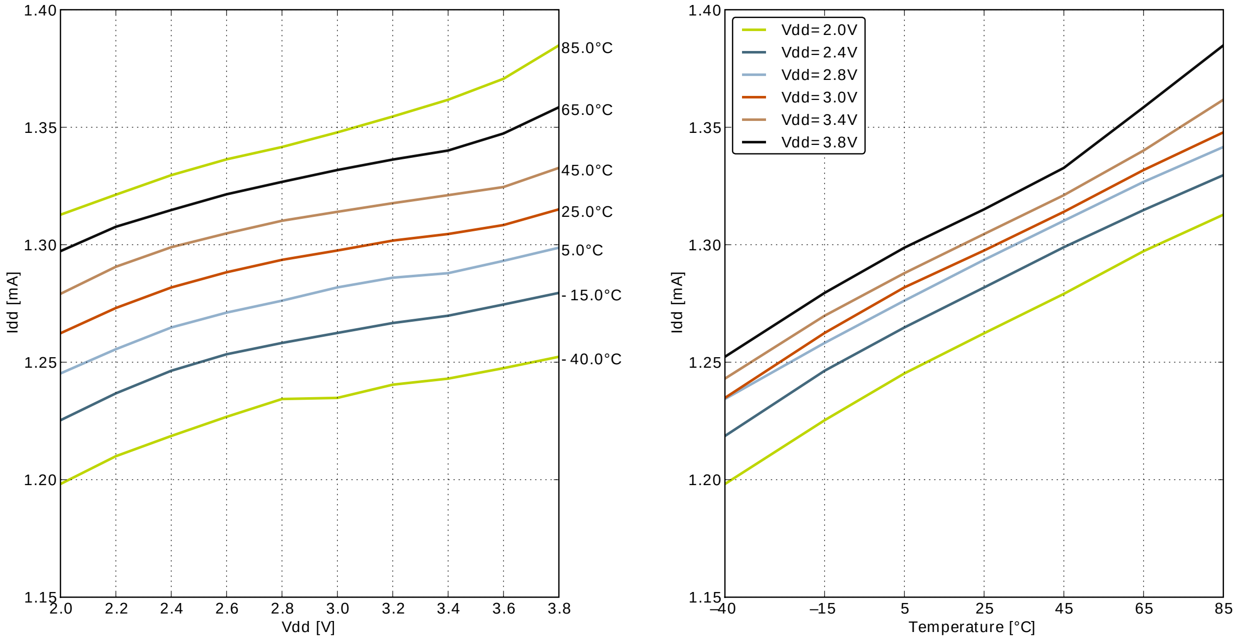


Figure 3.7. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 21 MHz

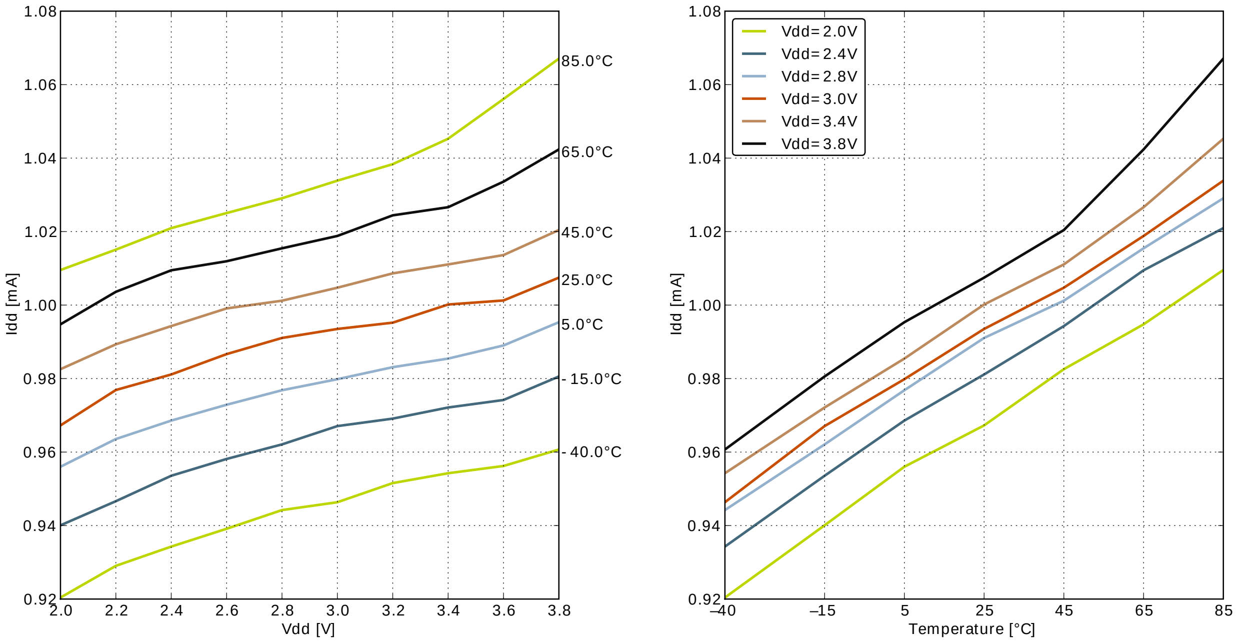


Figure 3.8. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 14 MHz

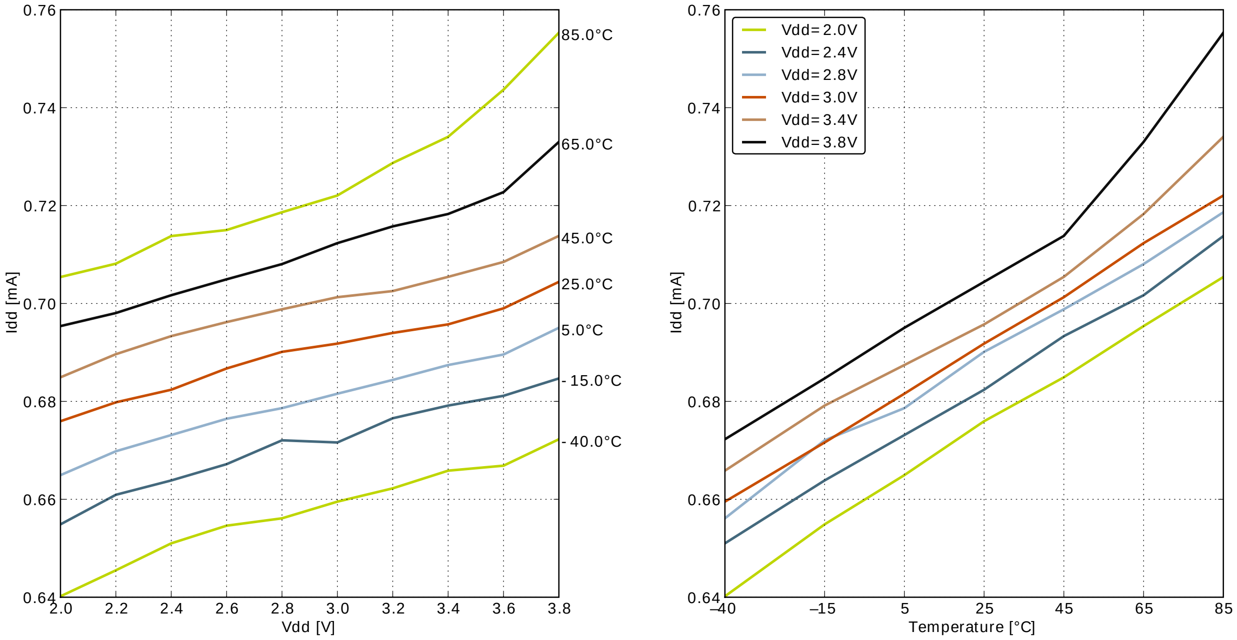


Figure 3.9. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 11 MHz

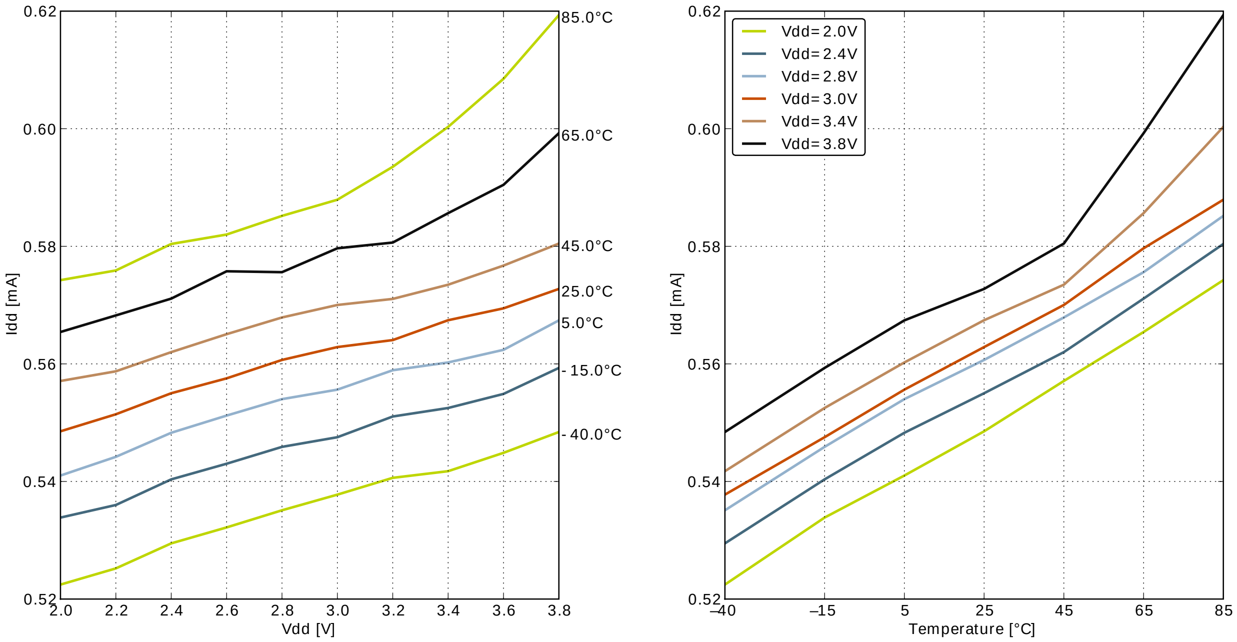
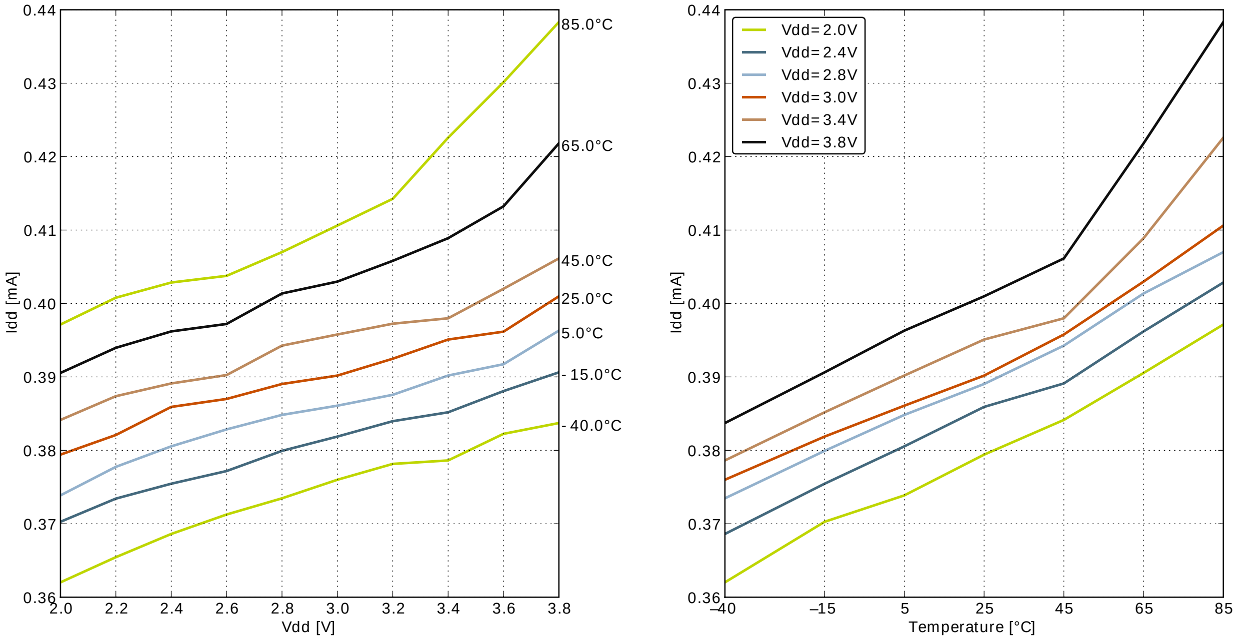
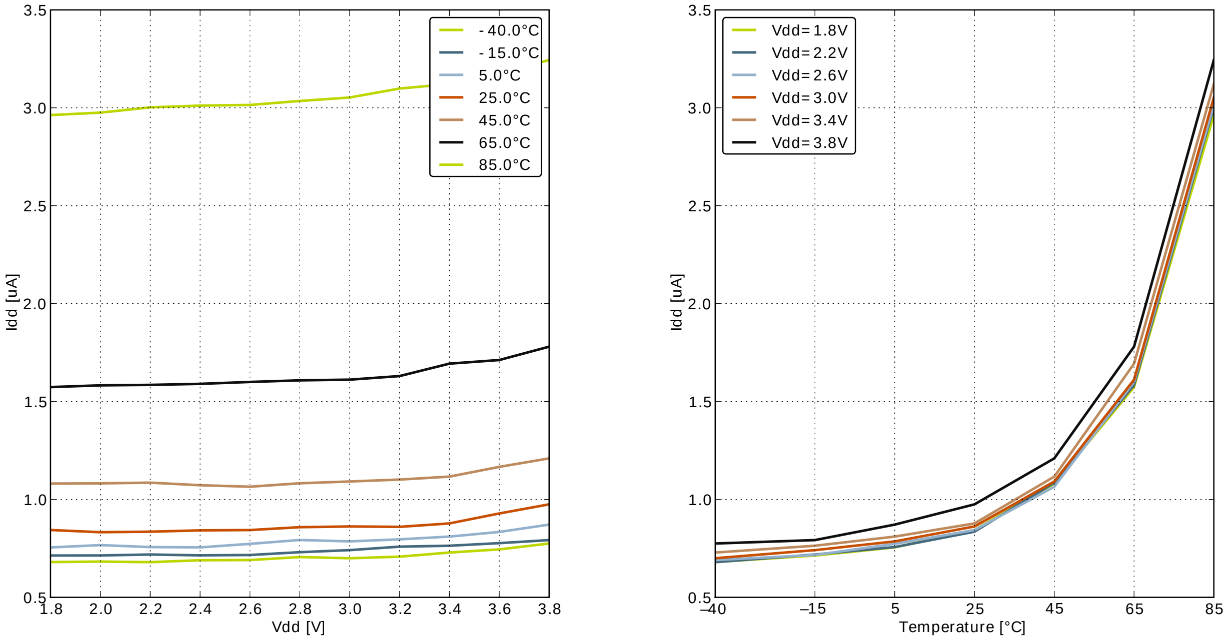


Figure 3.10. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 7 MHz



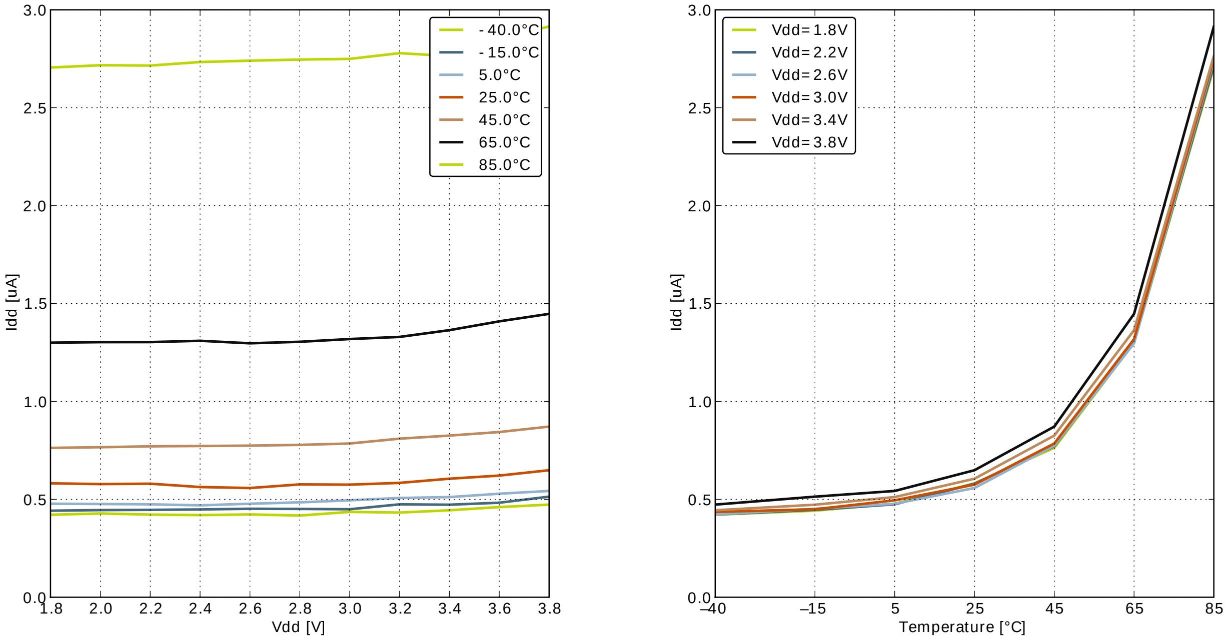
3.4.3 EM2 Current Consumption

Figure 3.11. EM2 current consumption. RTC prescaled to 1kHz, 32.768 kHz LFRCO.



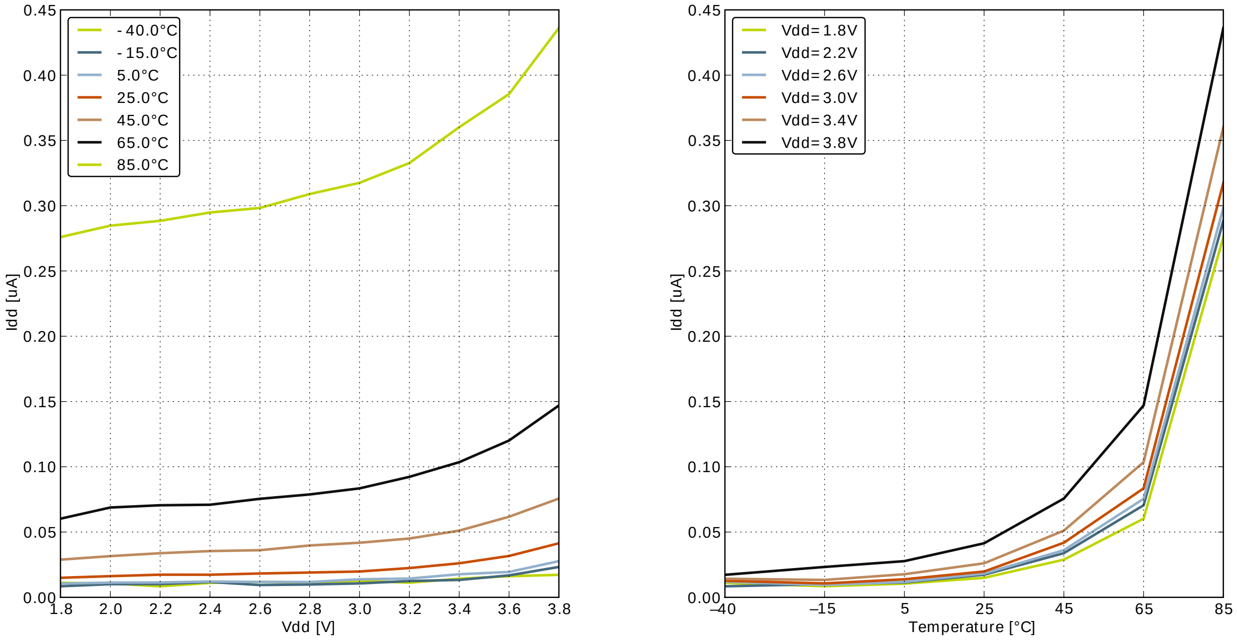
3.4.4 EM3 Current Consumption

Figure 3.12. EM3 current consumption.



3.4.5 EM4 Current Consumption

Figure 3.13. EM4 current consumption.



3.5 Transition between Energy Modes

The transition times are measured from the trigger to the first clock edge in the CPU.

Table 3.4. Energy Modes Transitions

Symbol	Parameter	Min	Typ	Max	Unit
t_{EM10}	Transition time from EM1 to EM0		0		HF-CORE-CLK cycles
t_{EM20}	Transition time from EM2 to EM0		2		µs
t_{EM30}	Transition time from EM3 to EM0		2		µs
t_{EM40}	Transition time from EM4 to EM0		163		µs

3.6 Power Management

The EFM32G requires the AVDD_x, VDD_DREG and IOVDD_x pins to be connected together (with optional filter) at the PCB level. For practical schematic recommendations, please see the application note, "AN0002 EFM32 Hardware Design Considerations".

Table 3.5. Power Management

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$V_{BODextthr-}$	BOD threshold on falling external supply voltage		1.74		1.96	V
$V_{BODextthr+}$	BOD threshold on rising external supply voltage			1.85		V
$V_{PORthr+}$	Power-on Reset (POR) threshold on rising external supply voltage				1.98	V
$t_{RESETdly}$	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		µs
t_{RESET}	negative pulse length to ensure complete reset of device		50			ns
$C_{DECOUPLE}$	Voltage regulator decoupling capacitor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		µF

3.7 Flash

Table 3.6. Flash

Symbol	Parameter	Condition	Min	Typ	Max	Unit
EC_{FLASH}	Flash erase cycles before failure		20000			cycles
RET_{FLASH}	Flash data retention	T_{AMB}<150°C	10000			h
		T_{AMB}<85°C	10			years
		T_{AMB}<70°C	20			years
t_{W_PROG}	Word (32-bit) programming time		20			µs
t_{P_ERASE}	Page erase time		20	20.4	20.8	ms
t_{D_ERASE}	Device erase time		40	40.8	41.6	ms
I_{ERASE}	Erase current				7[1]	mA
I_{WRITE}	Write current				7[1]	mA
V_{FLASH}	Supply voltage during flash erase and write		1.98		3.8	V

[1] Measured at 25°C

3.8 General Purpose Input Output

Table 3.7. GPIO

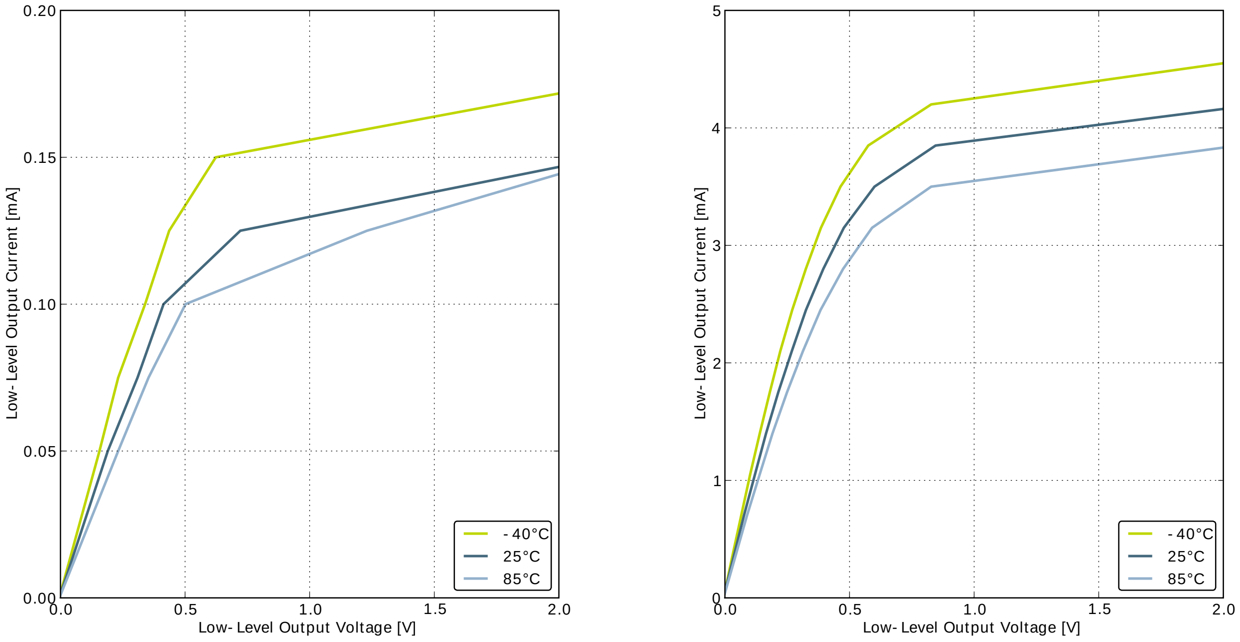
Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{IOIL}	Input low voltage				$0.30V_{DD}$[1]	V

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{IOIH}	Input high voltage		$0.70V_{DD}$[1]			V
V_{IOOH}	Output high voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.80V_{DD}$		V
		Sourcing 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.90V_{DD}$		V
		Sourcing 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.85V_{DD}$		V
		Sourcing 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.90V_{DD}$		V
		Sourcing 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	$0.75V_{DD}$			V
		Sourcing 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	$0.85V_{DD}$			V
		Sourcing 20 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	$0.60V_{DD}$			V
		Sourcing 20 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	$0.80V_{DD}$			V
V_{IOOL}	Output low voltage (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sinking 0.1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.20V_{DD}$		V
		Sinking 0.1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		$0.10V_{DD}$		V
		Sinking 1 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.10V_{DD}$		V
		Sinking 1 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		$0.05V_{DD}$		V
		Sinking 6 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			$0.30V_{DD}$	V
		Sinking 6 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			$0.20V_{DD}$	V
		Sinking 20 mA, V_{DD}=1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			$0.35V_{DD}$	V
		Sinking 20 mA, V_{DD}=3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH			$0.25V_{DD}$	V
I_{IOLEAK}	Input leakage current	High Impedance IO connected to GROUND or V_{DD}		±0.1	±40	nA

Symbol	Parameter	Condition	Min	Typ	Max	Unit
R_{PU}	I/O pin pull-up resistor			40		kOhm
R_{PD}	I/O pin pull-down resistor			40		kOhm
R_{IOESD}	Internal ESD series resistor			200		Ohm
$t_{IOGLITCH}$	Pulse width of pulses to be removed by the glitch suppression filter		10		50	ns
t_{IOOF}	Output fall time	GPIO_Px_CTRL DRIVEMODE = LOWEST and load capacitance C_L=12.5-25pF.	20+0.1C_L		250	ns
		GPIO_Px_CTRL DRIVEMODE = LOW and load capacitance C_L=350-600pF	20+0.1C_L		250	ns
V_{IOHYST}	I/O pin hysteresis (V_{IOTHR+} - V_{IOTHR-})	V_{DD} = 1.98 - 3.8 V	0.1V_{DD}			V

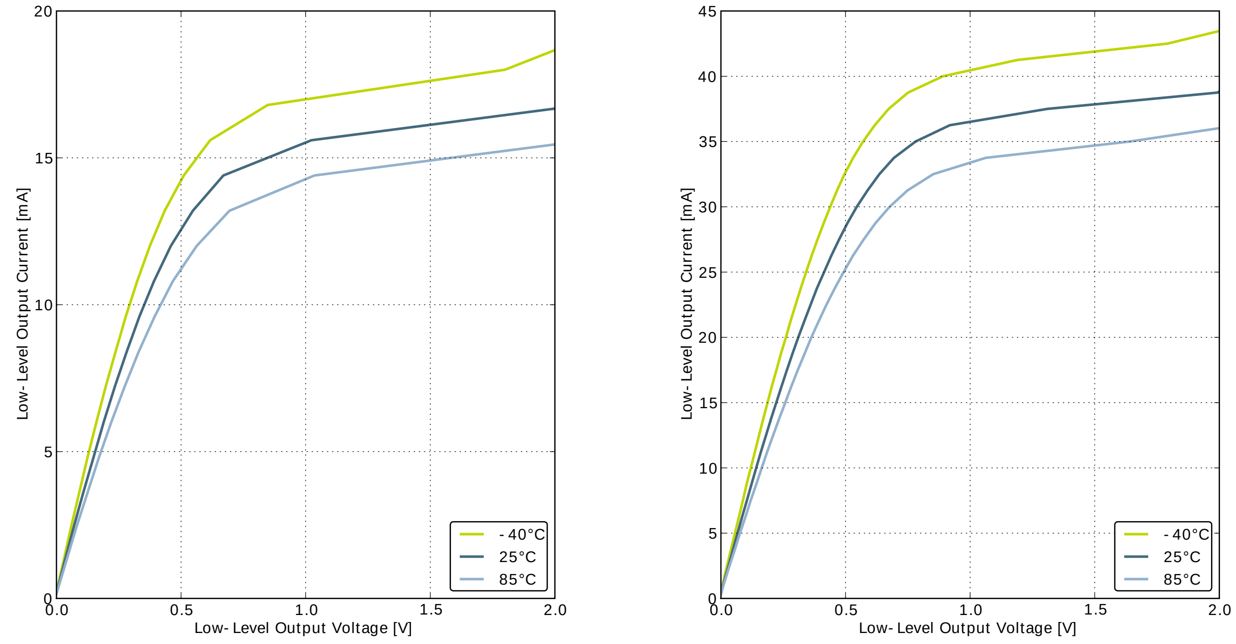
[1] If the GPIO input voltage is between 0.3V_{DD} and 0.7V_{DD}, the current consumption will increase.

Figure 3.14. Typical Low-Level Output Current, 2V Supply Voltage



GPIO_Px_CTRL DRIVEMODE = LOWEST

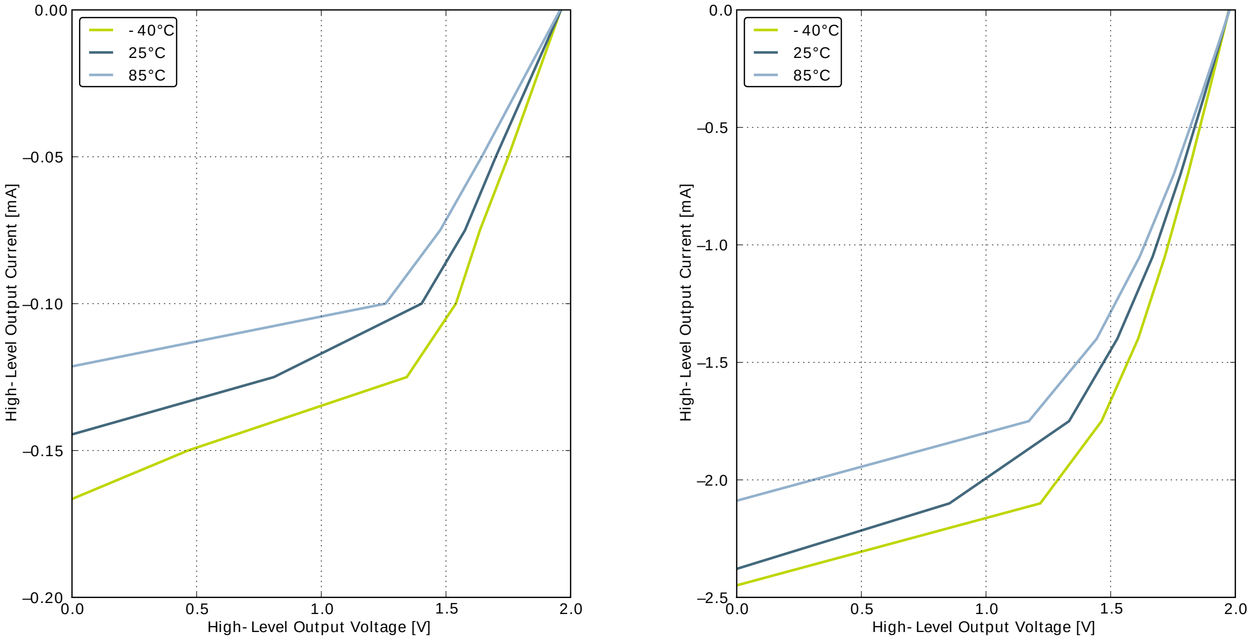
GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD

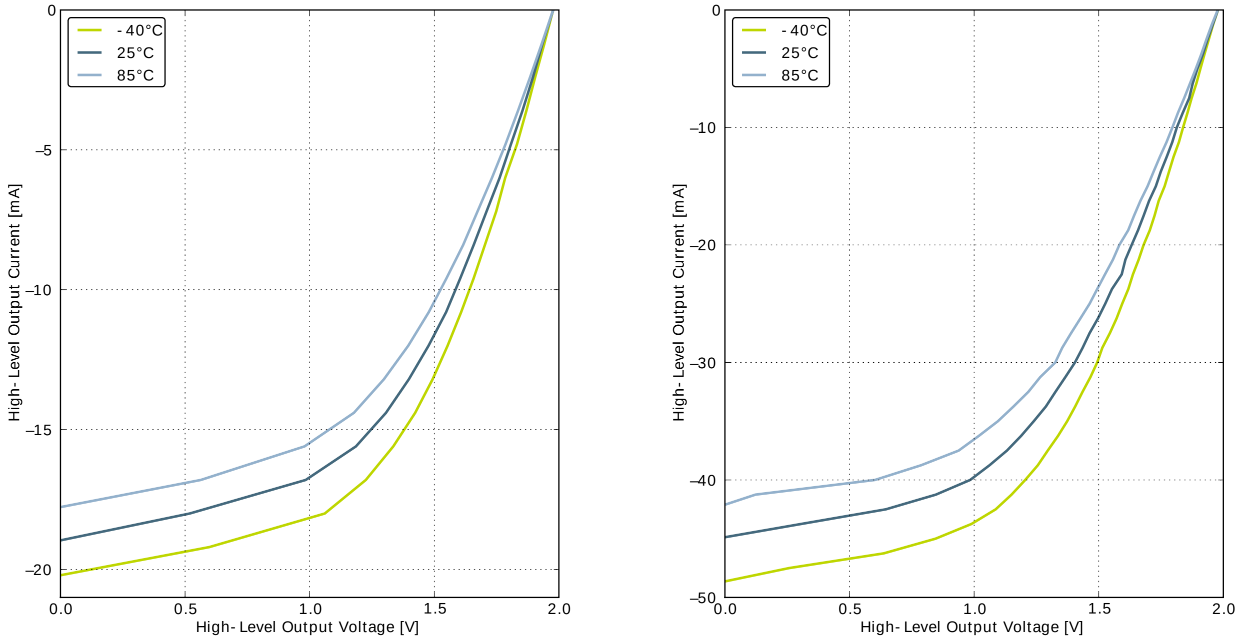
GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.15. Typical High-Level Output Current, 2V Supply Voltage



GPIO_Px_CTRL DRIVEMODE = LOWEST

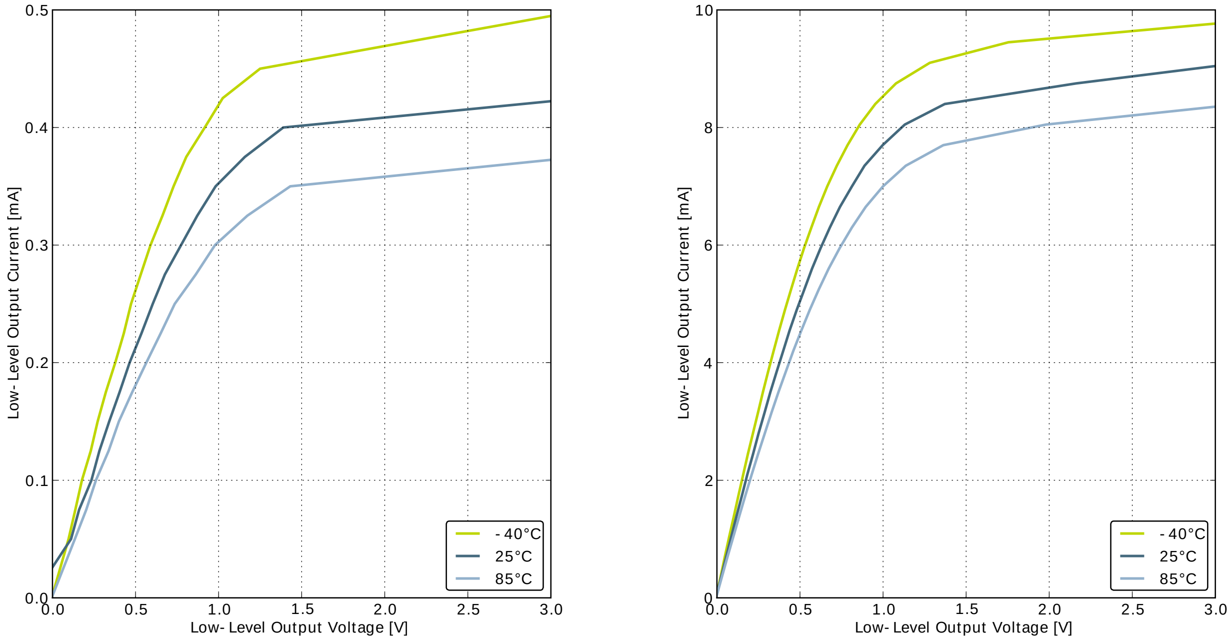
GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD

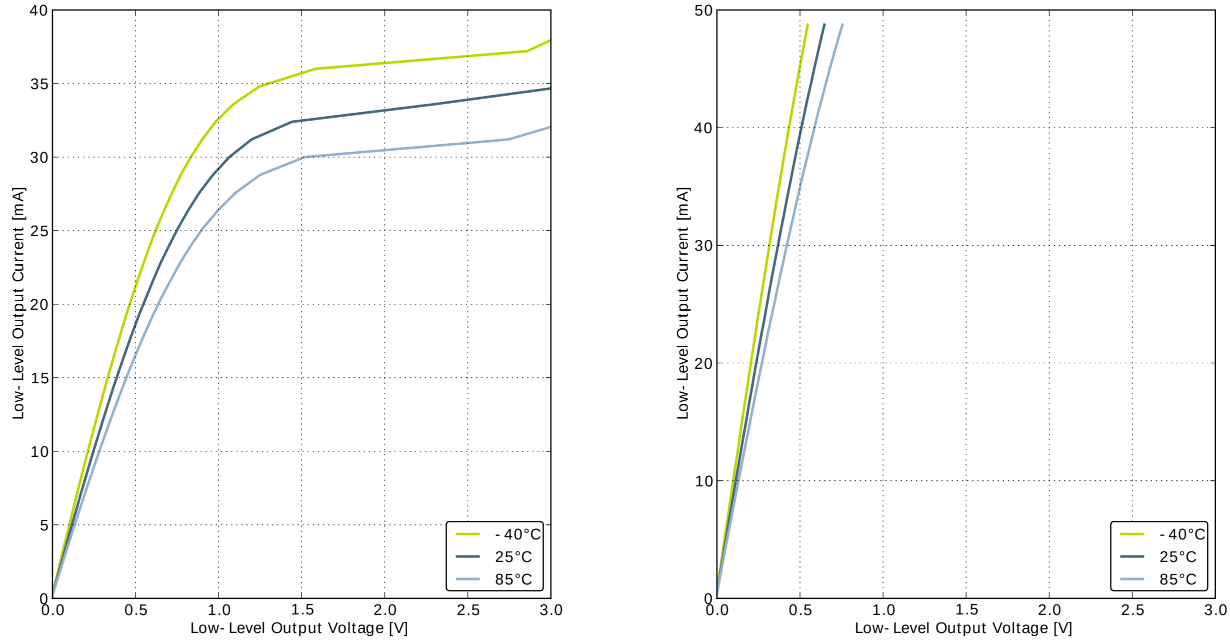
GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.16. Typical Low-Level Output Current, 3V Supply Voltage



GPIO_Px_CTRL DRIVEMODE = LOWEST

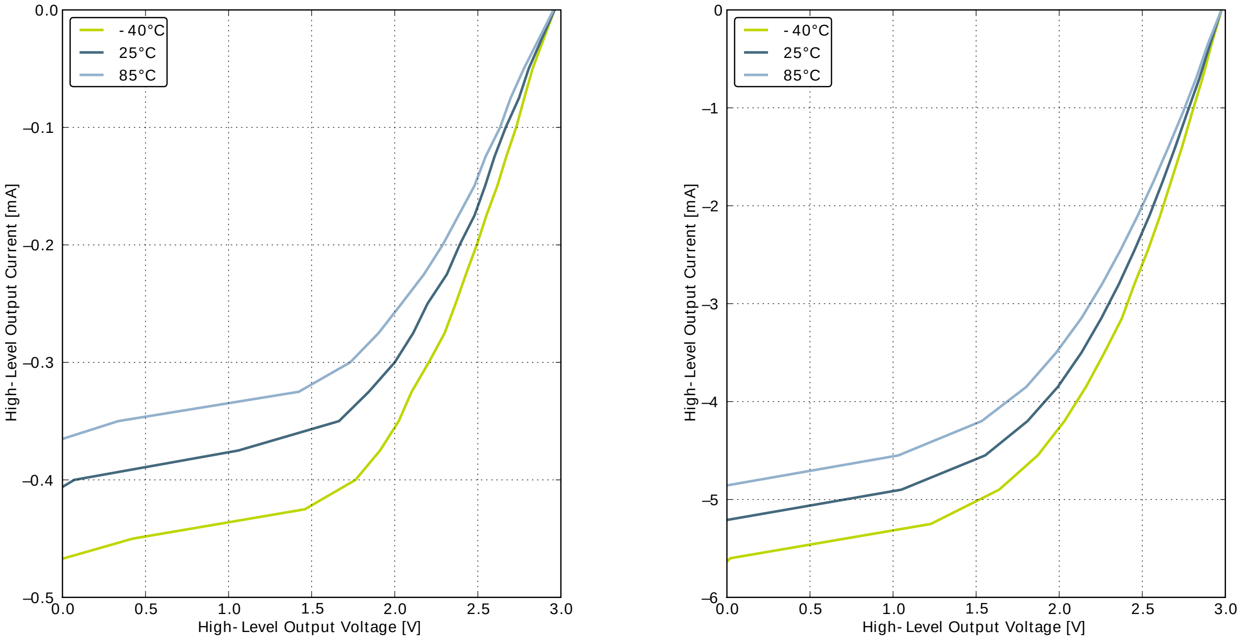
GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD

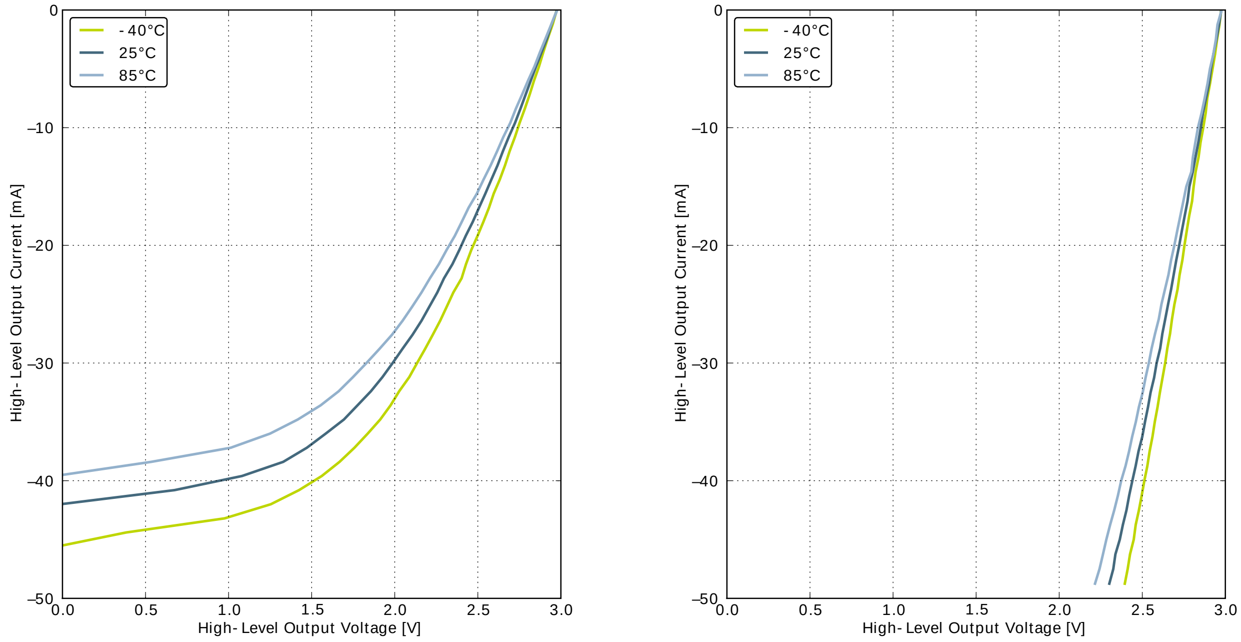
GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.17. Typical High-Level Output Current, 3V Supply Voltage



GPIO_Px_CTRL DRIVEMODE = LOWEST

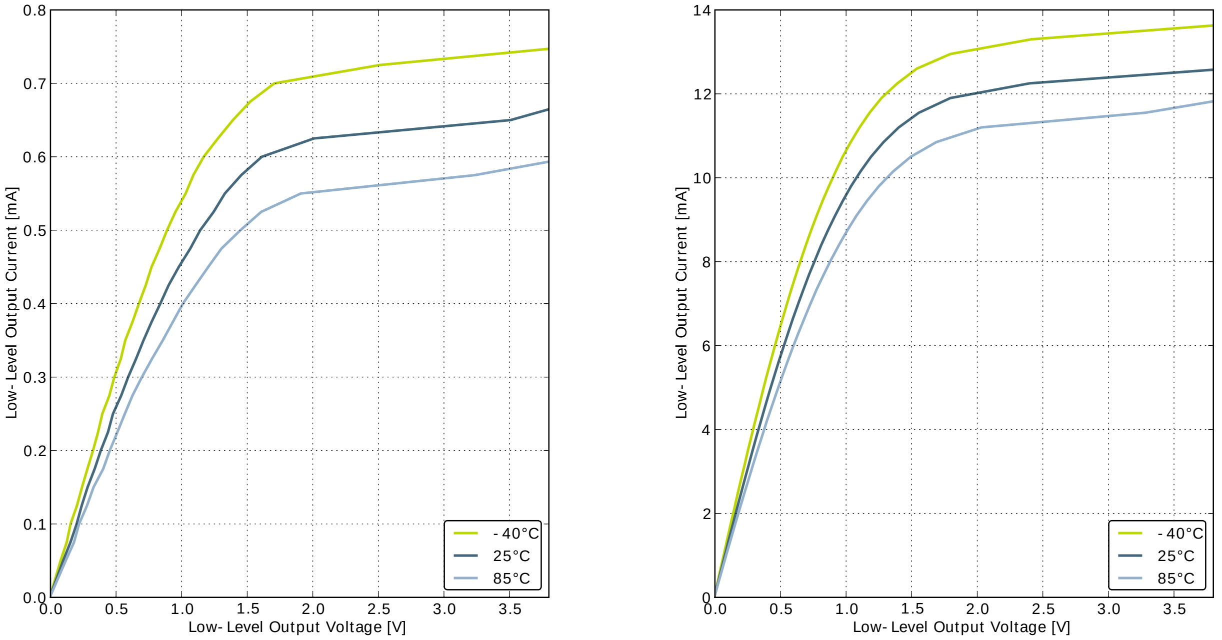
GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD

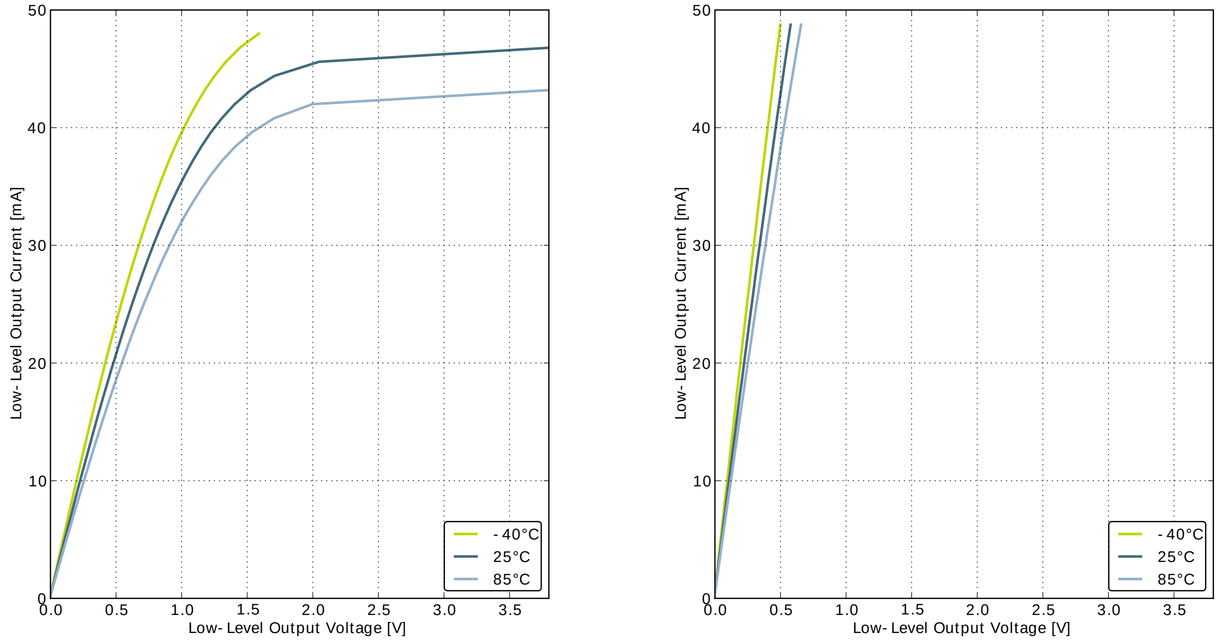
GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.18. Typical Low-Level Output Current, 3.8V Supply Voltage



GPIO_Px_CTRL DRIVEMODE = LOWEST

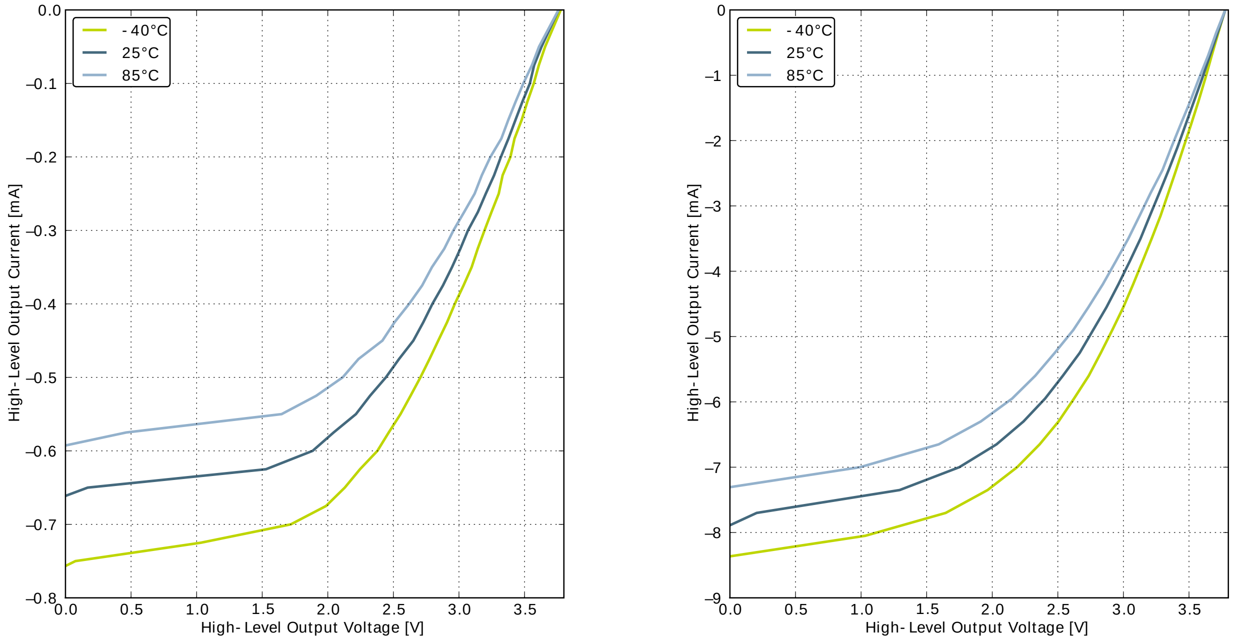
GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD

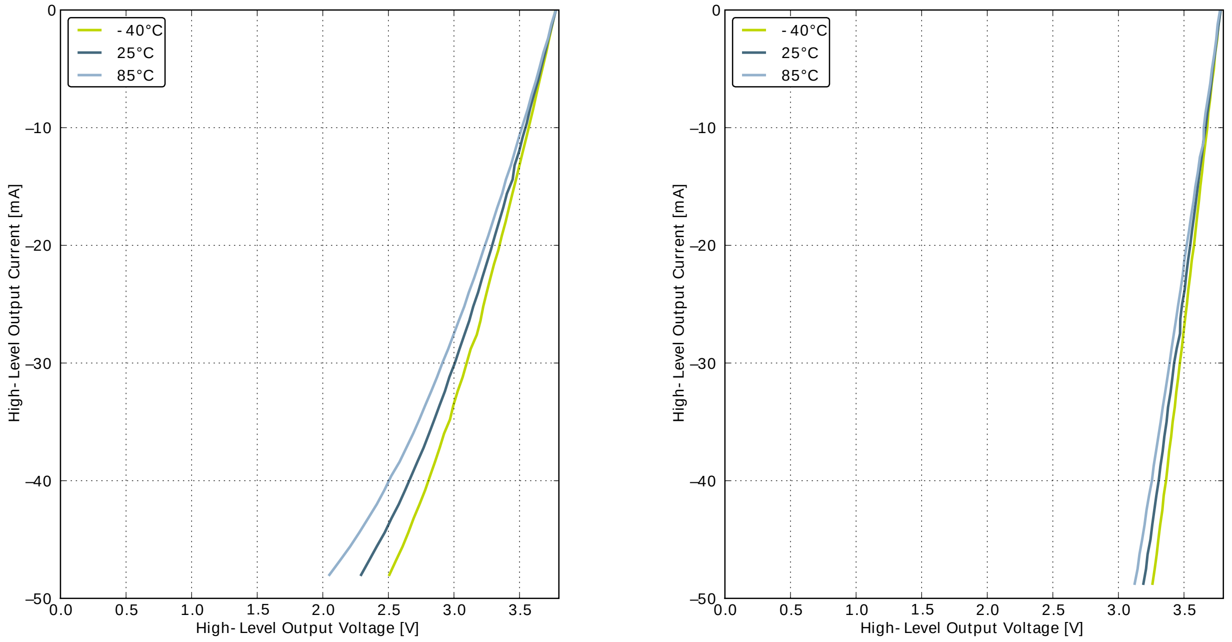
GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.19. Typical High-Level Output Current, 3.8V Supply Voltage



GPIO_Px_CTRL DRIVEMODE = LOWEST

GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD

GPIO_Px_CTRL DRIVEMODE = HIGH

3.9 Oscillators

3.9.1 LFXO

Table 3.8. LFXO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFXO}	Supported nominal crystal frequency			32.768		kHz
ESR_{LFXO}	Supported crystal equivalent series resistance (ESR)			30	120	kOhm
C_{LFXOL}	Supported crystal external load range		X[1]		25	pF
I_{LFXO}	Current consumption for core and buffer after startup.	ESR=30 kOhm, C_L=10 pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t_{LFXO}	Start- up time.	ESR=30 kOhm, C_L=10 pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		400		ms

[1] See Minimum Load Capacitance (C_{LFXOL}) Requirement For Safe Crystal Startup in Configurator in Simplicity Studio

For safe startup of a given crystal, the Configurator tool in Simplicity Studio contains a tool to help users configure both load capacitance and software settings for using the LFXO. For details regarding the crystal configuration, the reader is referred to application note "AN0016 EFM32 Oscillator Design Consideration".

3.9.2 HFXO

Table 3.9. HFXO

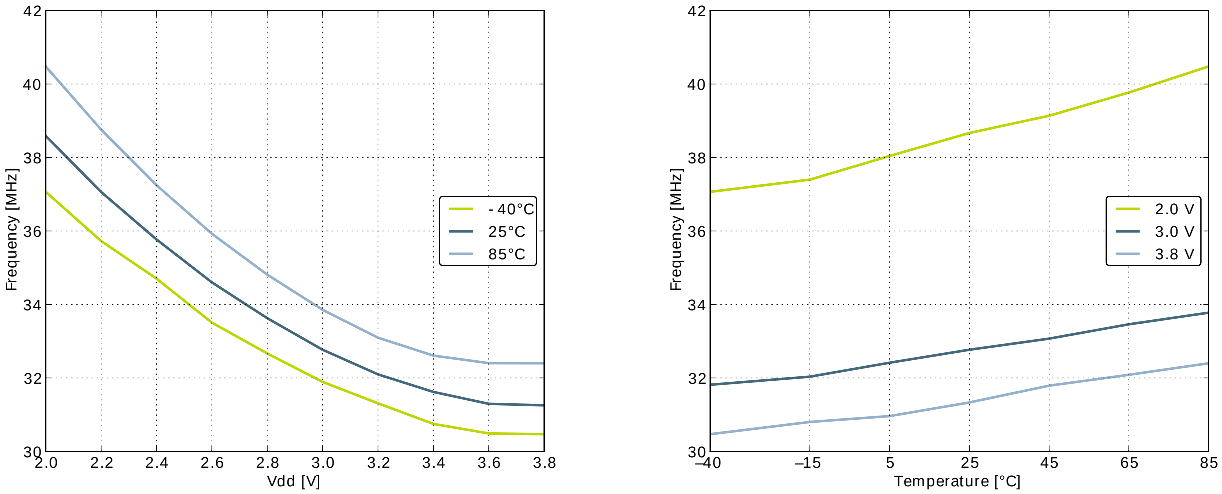
Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFXO}	Supported nominal crystal Frequency		4		32	MHz
ESR_{HFXO}	Supported crystal equivalent series resistance (ESR)	Crystal frequency 32 MHz		30	60	Ohm
		Crystal frequency 4 MHz		400	1500	Ohm
g_{mHFXO}	The transconductance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C_{HFXOL}	Supported crystal external load range		5		25	pF
I_{HFXO}	Current consumption for HFXO after startup	4 MHz: ESR=400 Ohm, C_L=20 pF, HFXOBOOST in CMU_CTRL equals 0b11		85		µA
		32 MHz: ESR=30 Ohm, C_L=10 pF, HFXOBOOST in CMU_CTRL equals 0b11		165		µA
t_{HFXO}	Startup time	32 MHz: ESR=30 Ohm, C_L=10 pF, HFXOBOOST in CMU_CTRL equals 0b11		400		µs
	Pulse width removed by glitch detector		1		4	ns

3.9.3 LFRCO

Table 3.10. LFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFRCO}	Oscillation frequency , V_{DD}= 3.0 V, T_{AMB}=25°C		31.29	32.768	34.24	kHz
t_{LFRCO}	Startup time not including software calibration			150		µs
I_{LFRCO}	Current consumption			190		nA
TC_{LFRCO}	Temperature coefficient			±0.02		%/°C
VC_{LFRCO}	Supply voltage coefficient			±15		%/V
$TUNESTEP_{LFRCO}$	Frequency step for LSB change in TUNING value			1.5		%

Figure 3.20. Calibrated LFRCO Frequency vs Temperature and Supply Voltage



3.9.4 HFRCO

Table 3.11. HFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{HFRCO}	Oscillation frequency, V_{DD}= 3.0 V, T_{AMB}=25°C	28 MHz frequency band	27.16	28	28.84	MHz
		21 MHz frequency band	20.37	21	21.63	MHz
		14 MHz frequency band	13.58	14	14.42	MHz
		11 MHz frequency band	10.67	11	11.33	MHz
		7 MHz frequency band	6.402	6.6[1]	6.798	MHz
		1 MHz frequency band	1.164	1.2[2]	1.236	MHz
$t_{HFRCO\_settling}$	Settling time after start-up	f_{HFRCO} = 14 MHz		0.6		Cycles
	Settling time after band switch			25		Cycles
I_{HFRCO}	Current consumption (Production test condition = 14 MHz)	f_{HFRCO} = 28 MHz		106	190	µA
		f_{HFRCO} = 21 MHz		93	155	µA
		f_{HFRCO} = 14 MHz		77	120	µA
		f_{HFRCO} = 11 MHz		72	110	µA
		f_{HFRCO} = 6.6 MHz		63	90	µA
		f_{HFRCO} = 1.2 MHz		22	32	µA
DC_{HFRCO}	Duty cycle	f_{HFRCO} = 14 MHz	48.5	50	51	%
$TUNESTEP_{HFRCO}$	Frequency step for LSB change in TUNING value			0.3[3]		%

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[1] For devices with prod. rev. < 19, Typ = 7MHz and Min/Max values not applicable.

[2] For devices with prod. rev. < 19, Typ = 1MHz and Min/Max values not applicable.

[3] The TUNING field in the CMU_HFRCOCTRL register may be used to adjust the HFRCO frequency. There is enough adjustment range to ensure that the frequency bands above 7 MHz will always have some overlap across supply voltage and temperature. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the HFRCO frequency at any arbitrary value between 7 MHz and 28 MHz across operating conditions.

Figure 3.21. Calibrated HFRCO 1 MHz Band Frequency vs Supply Voltage and Temperature

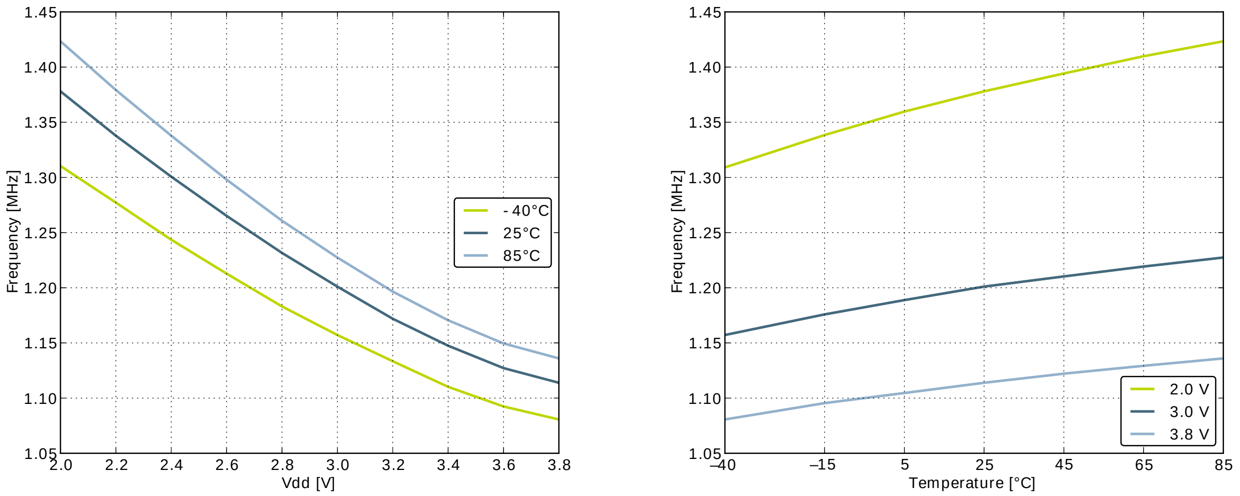


Figure 3.22. Calibrated HFRCO 7 MHz Band Frequency vs Supply Voltage and Temperature

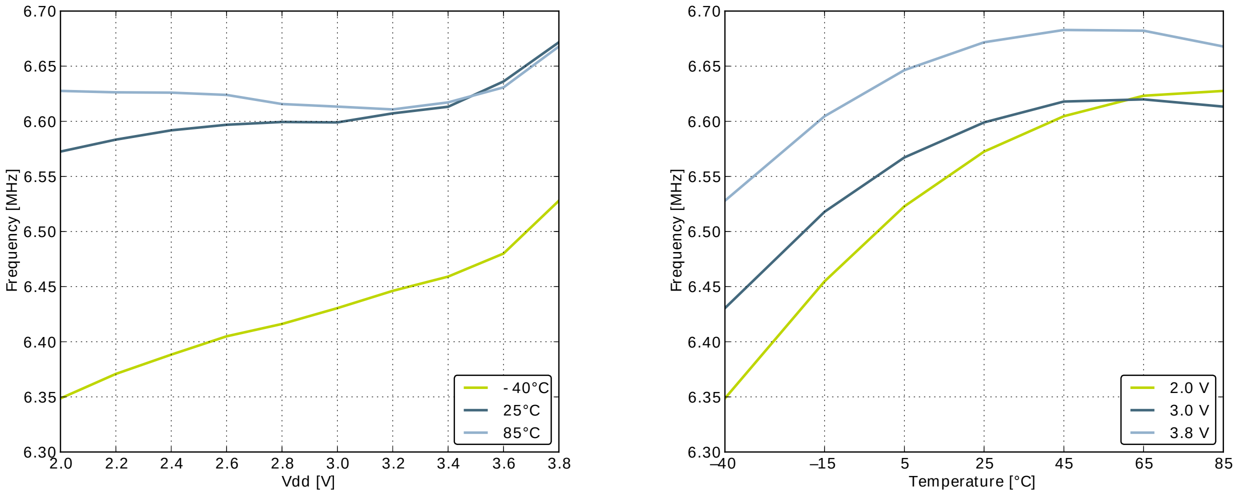


Figure 3.23. Calibrated HFRCO 11 MHz Band Frequency vs Supply Voltage and Temperature

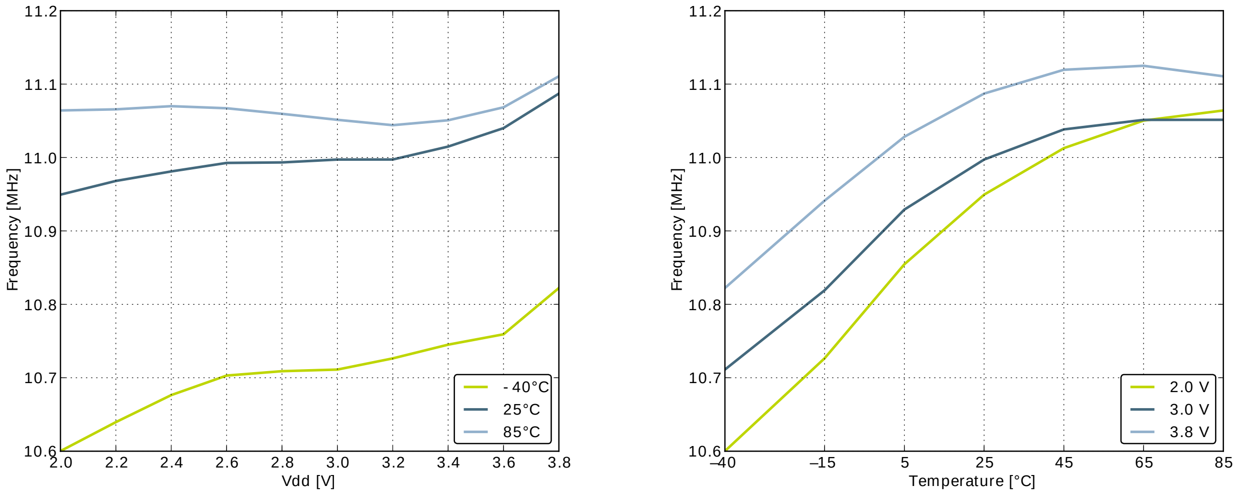


Figure 3.24. Calibrated HFRCO 14 MHz Band Frequency vs Supply Voltage and Temperature

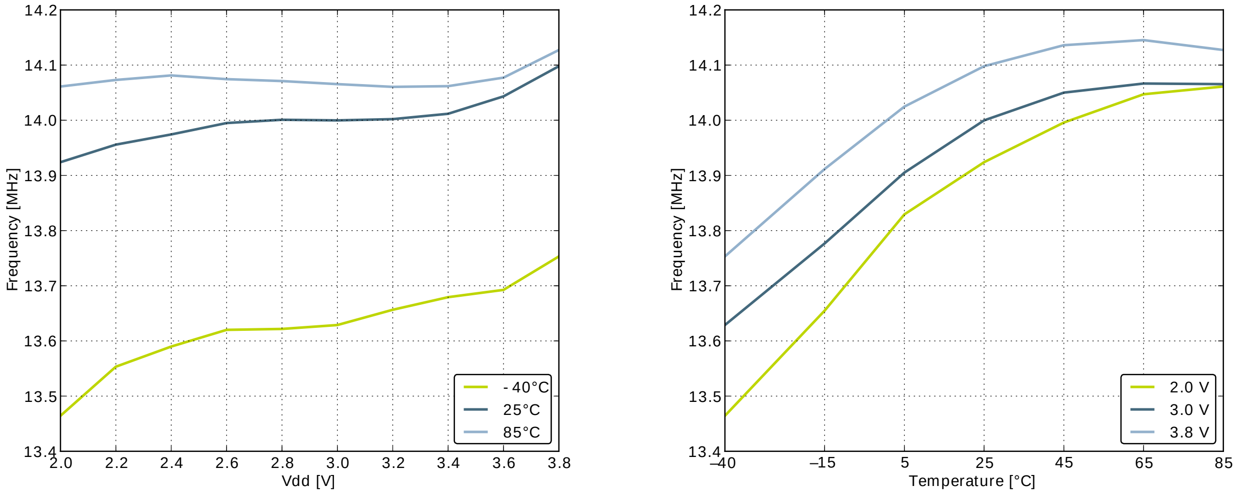


Figure 3.25. Calibrated HFRCO 21 MHz Band Frequency vs Supply Voltage and Temperature

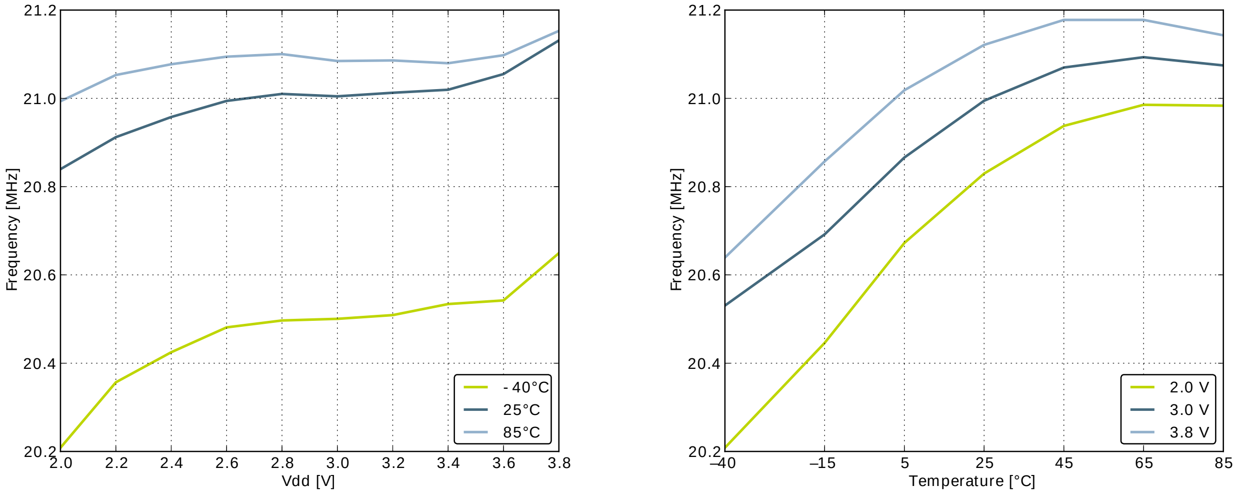
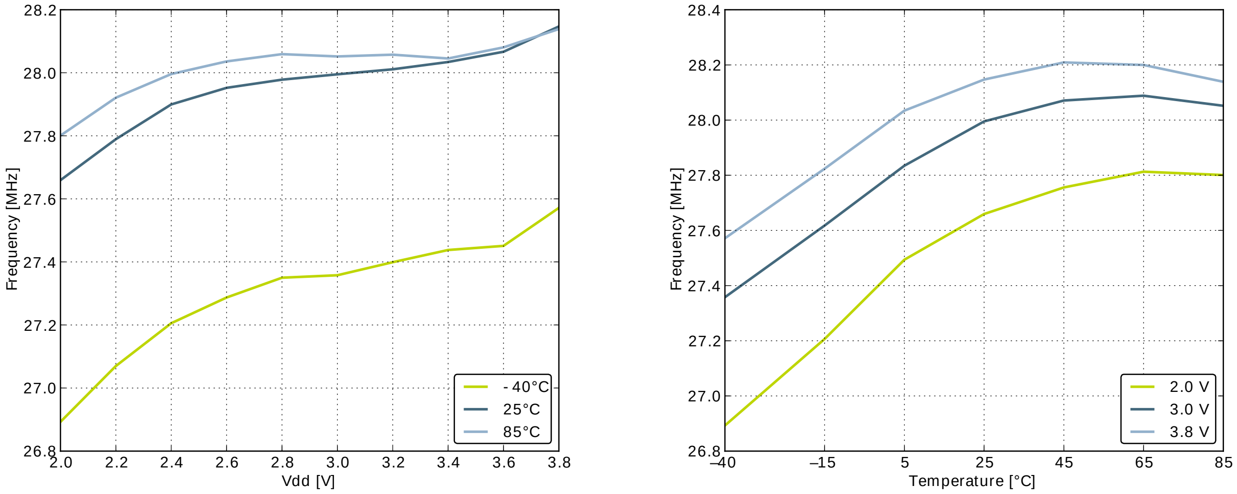


Figure 3.26. Calibrated HFRCO 28 MHz Band Frequency vs Supply Voltage and Temperature



3.9.5 AUXHFRCO

Table 3.12. AUXHFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$f_{AUXHFRCO}$	Oscillation frequency, V_{DD}= 3.0 V, T_{AMB}=25°C	14 MHz frequency band	13.580	14.0	14.420	MHz
$t_{AUXHFRCO\_settling}$	Settling time after start-up	$f_{AUXHFRCO}$ = 14 MHz		0.6		Cycles
$DC_{AUXHFRCO}$	Duty cycle	$f_{AUXHFRCO}$ = 14 MHz	48.5	50	51	%
$TUNESTEP_{AUXHFRCO}$	Frequency step for LSB change in TUNING value			0.3[1]		%

[1] The TUNING field in the CMU_AUXHFRCOCTRL register may be used to adjust the AUXHFRCO frequency. By using a stable frequency reference such as the LFXO or HFXO, a firmware calibration routine can vary the TUNING bits and the frequency band to maintain the AUXHFRCO frequency at any arbitrary value in the 14 MHz range across operating conditions.

3.9.6 ULFRCO

Table 3.13. ULFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{ULFRCO}	Oscillation frequency	25°C, 3V	0.70		1.75	kHz
TC_{ULFRCO}	Temperature coefficient			0.05		%/°C
VC_{ULFRCO}	Supply voltage coefficient			-18.2		%/V

3.10 Analog Digital Converter (ADC)

Table 3.14. ADC

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{ADCIN}	Input voltage range	Single ended	0		V_{REF}	V
		Differential	$-V_{REF}/2$		$V_{REF}/2$	V
$V_{ADCREFIN}$	Input range of external reference voltage, single ended and differential		1.25		V_{DD}	V
$V_{ADCREFIN\_CH7}$	Input range of external negative reference voltage on channel 7	See $V_{ADCREFIN}$	0		V_{DD} - 1.1	V
$V_{ADCREFIN\_CH6}$	Input range of external positive reference voltage on channel 6	See $V_{ADCREFIN}$	0.625		V_{DD}	V
$V_{ADCCMIN}$	Common mode input range		0		V_{DD}	V
I_{ADCIN}	Input current	2pF sampling capacitors		<100		nA

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$CMRR_{ADC}$	Analog input common mode rejection ratio			65		dB
I_{ADC}	Average active current	1 MSamples/s, 12 bit, external reference		351		µA
		1 MSamples/s, 12 bit, internal reference		411		µA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUPMODE in ADCn_CTRL set to 0b00, ADC_CLK running at 13MHz		67		µA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUPMODE in ADCn_CTRL set to 0b01, ADC_CLK running at 13MHz		63		µA
		10 kSamples/s 12 bit, internal 1.25 V reference, WARMUPMODE in ADCn_CTRL set to 0b10, ADC_CLK running at 13MHz		64		µA
C_{ADCIN}	Input capacitance			2		pF
R_{ADCIN}	Input ON resistance		1			MOhm
$R_{ADCFILT}$	Input RC filter resistance			10		kOhm
$C_{ADCFILT}$	Input RC filter/decoupling capacitance			250		fF
f_{ADCCLK}	ADC Clock Frequency				13	MHz
$t_{ADCCONV}$	Conversion time	6 bit	7			ADCCLK Cycles
		8 bit	11			ADCCLK Cycles
		12 bit	13			ADCCLK Cycles
t_{ADCACQ}	Acquisition time	Programmable	1		256	ADCCLK Cycles
$t_{ADCACQVDD3}$	Required acquisition time for VDD/3 reference		2			µs
$t_{ADCSTART}$	Startup time of reference generator and ADC core in NORMAL mode			5		µs
	Startup time of reference generator and ADC core in			1		µs

Symbol	Parameter	Condition	Min	Typ	Max	Unit
	KEEPADCWARM mode					
SNR_{ADC}	Signal to Noise Ratio (SNR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		59		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		65		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		65		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V_{DD} reference		67		dB
		1 MSamples/s, 12 bit, differential, $2xV_{DD}$ reference		69		dB
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		63		dB
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		67		dB
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V_{DD} reference	63	69		dB
		200 kSamples/s, 12 bit, differential, $2xV_{DD}$ reference		70		dB
$SINAD_{ADC}$	SIgnal-to-Noise And Distortion-ratio (SINAD)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		58		dB
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		62		dB
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		64		dB
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		60		dB
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		64		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		1 MSamples/s, 12 bit, differential, V_{DD} reference		66		dB
		1 MSamples/s, 12 bit, differential, $2xV_{DD}$ reference		68		dB
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		61		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		65		dB
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		66		dB
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V_{DD} reference	62	68		dB
		200 kSamples/s, 12 bit, differential, $2xV_{DD}$ reference		69		dB
$SFDR_{ADC}$	Spurious-Free Dynamic Range (SFDR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		64		dBc
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		76		dBc
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		73		dBc
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		66		dBc
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		77		dBc
		1 MSamples/s, 12 bit, differential, V_{DD} reference		76		dBc
		1 MSamples/s, 12 bit, differential, $2xV_{DD}$ reference		75		dBc
		1 MSamples/s, 12 bit, differential, 5V reference		69		dBc
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		76		dBc
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		79		dBc
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		79		dBc

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		200 kSamples/s, 12 bit, differential, 5V reference		78		dBc
		200 kSamples/s, 12 bit, differential, V_{DD} reference	68	79		dBc
		200 kSamples/s, 12 bit, differential, 2xV_{DD} reference		79		dBc
$V_{ADCOFFSET}$	Offset voltage	After calibration, single ended	-4	0.3	4	mV
		After calibration, differential		0.3		mV
$TGRAD_{ADCTH}$	Thermometer output gradient			-1.92		mV/°C
				-6.3		ADC Codes/°C
DNL_{ADC}	Differential non-linearity (DNL)	V_{DD} = 3.0 V, external 2.5V reference	-1	±0.7	4	LSB
INL_{ADC}	Integral non-linearity (INL), End point method	V_{DD} = 3.0 V, external 2.5V reference		±1.2	±3	LSB
MC_{ADC}	No missing codes		11.999[1]	12		bits

[1] On the average every ADC will have one missing code, most likely to appear around 2048 ± n*512 where n can be a value in the set {-3, -2, -1, 1, 2, 3}. There will be no missing code around 2048, and in spite of the missing code the ADC will be monotonic at all times so that a response to a slowly increasing input will always be a slowly increasing output. Around the one code that is missing, the neighbour codes will look wider in the DNL plot. The spectra will show spurs on the level of -78dBc for a full scale input for chips that have the missing code issue.

The integral non-linearity (INL) and differential non-linearity parameters are explained in Figure 3.27 (p. 35) and Figure 3.28 (p. 36) , respectively.

Figure 3.27. Integral Non-Linearity (INL)

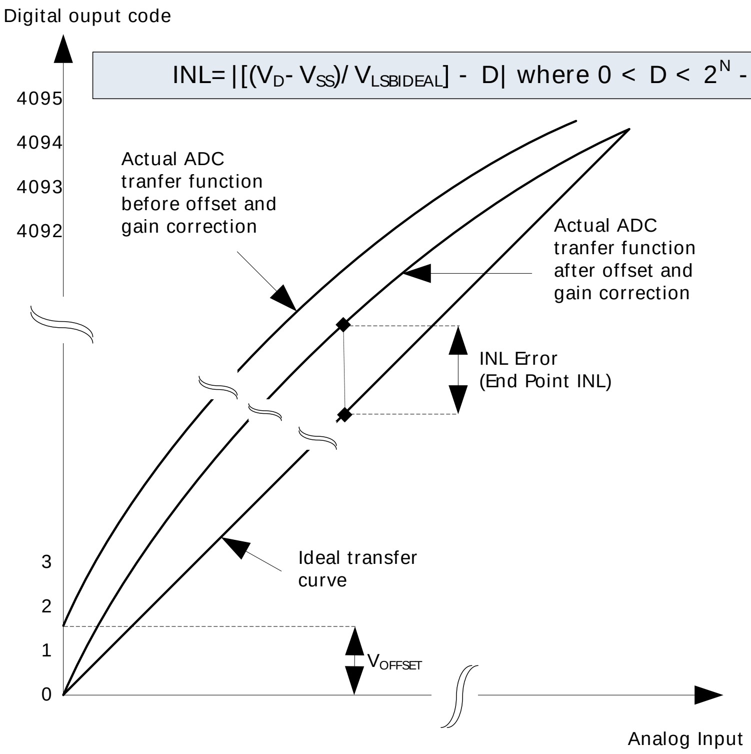
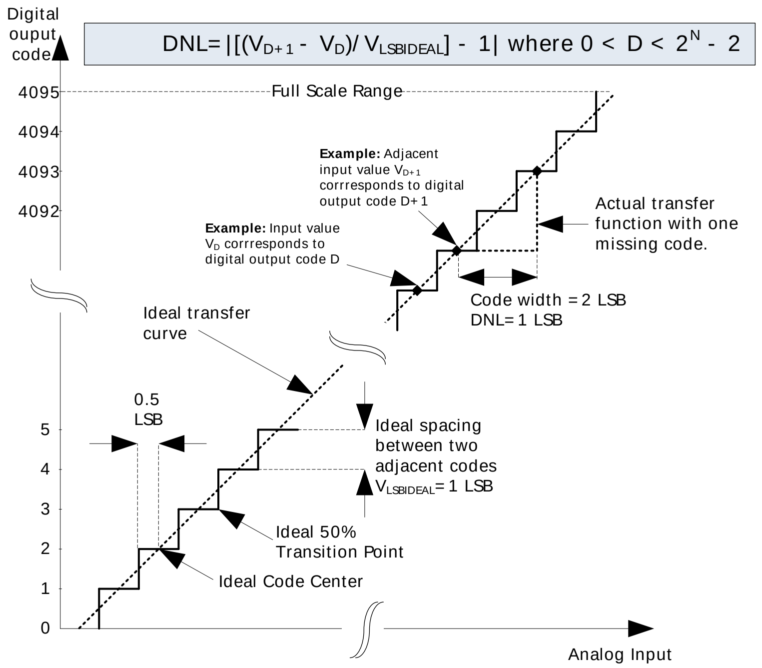
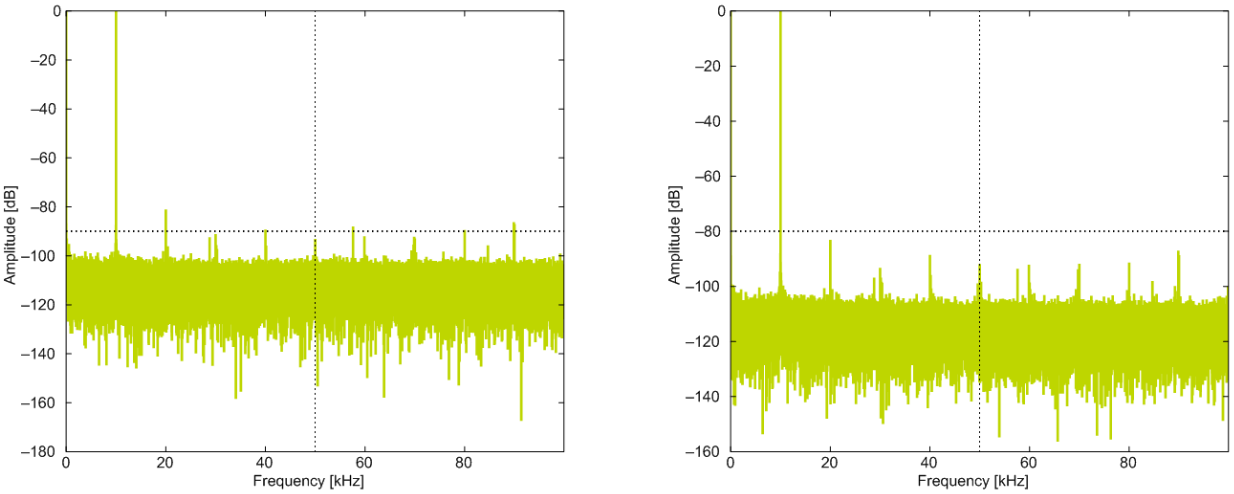


Figure 3.28. Differential Non-Linearity (DNL)



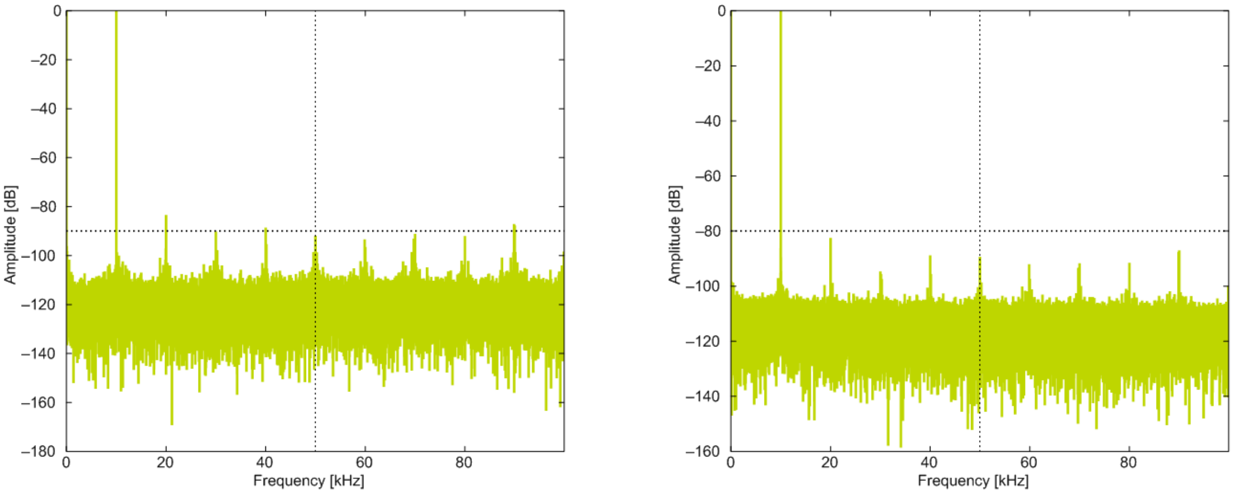
3.10.1 Typical performance

Figure 3.29. ADC Frequency Spectrum, Vdd = 3V, Temp = 25°C



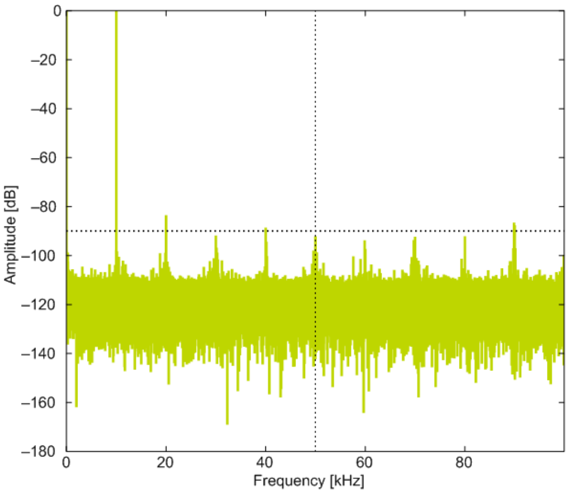
1.25V Reference

2.5V Reference



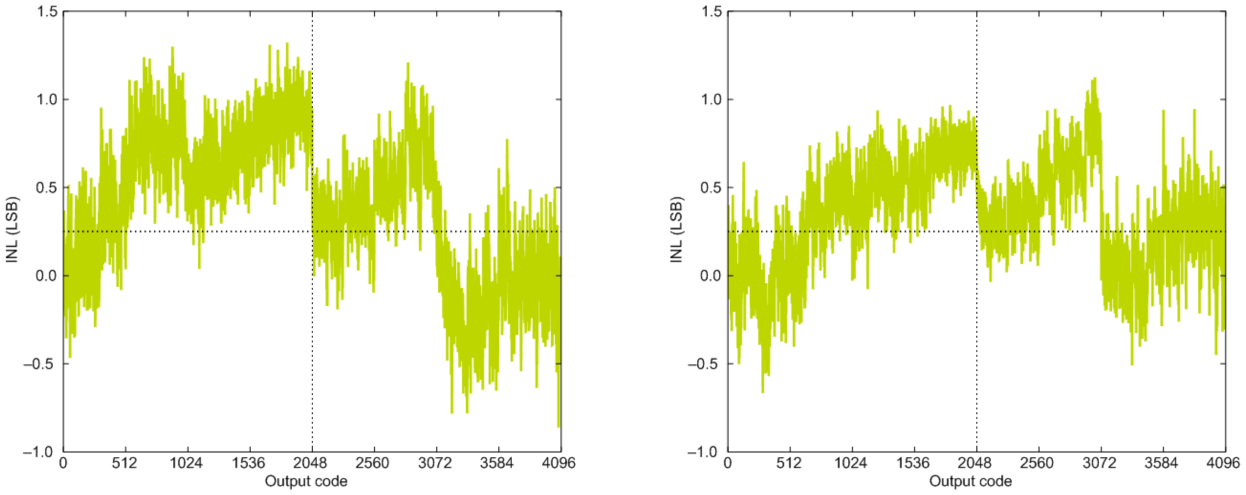
2XVDDVSS Reference

5VDIFF Reference



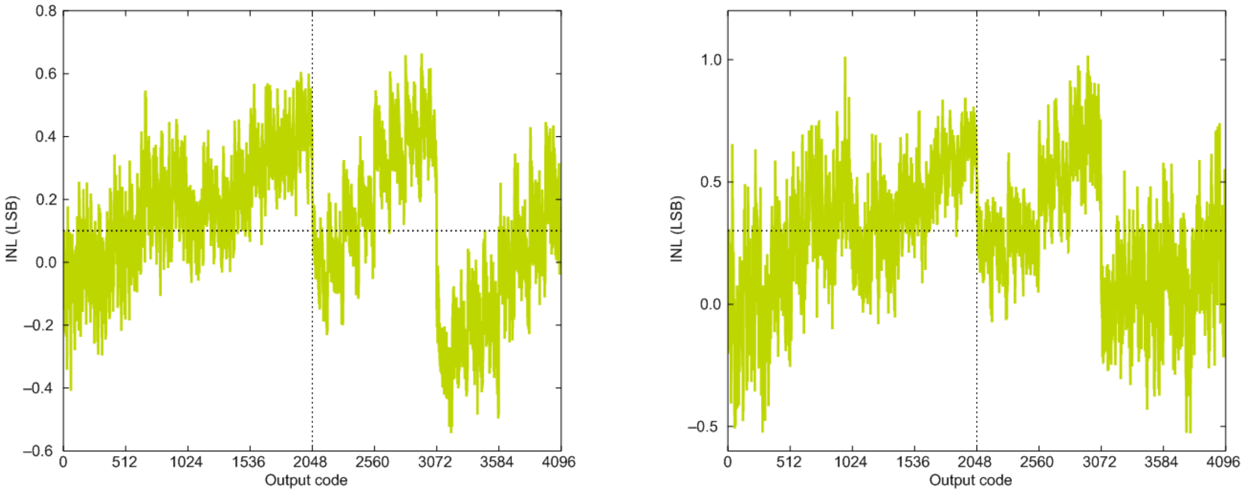
VDD Reference

Figure 3.30. ADC Integral Linearity Error vs Code, Vdd = 3V, Temp = 25°C



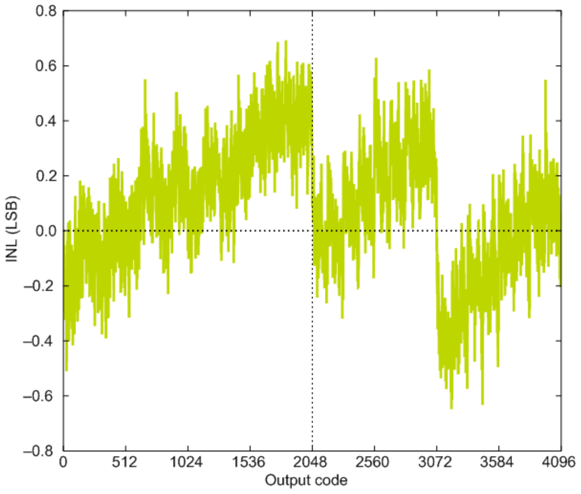
1.25V Reference

2.5V Reference



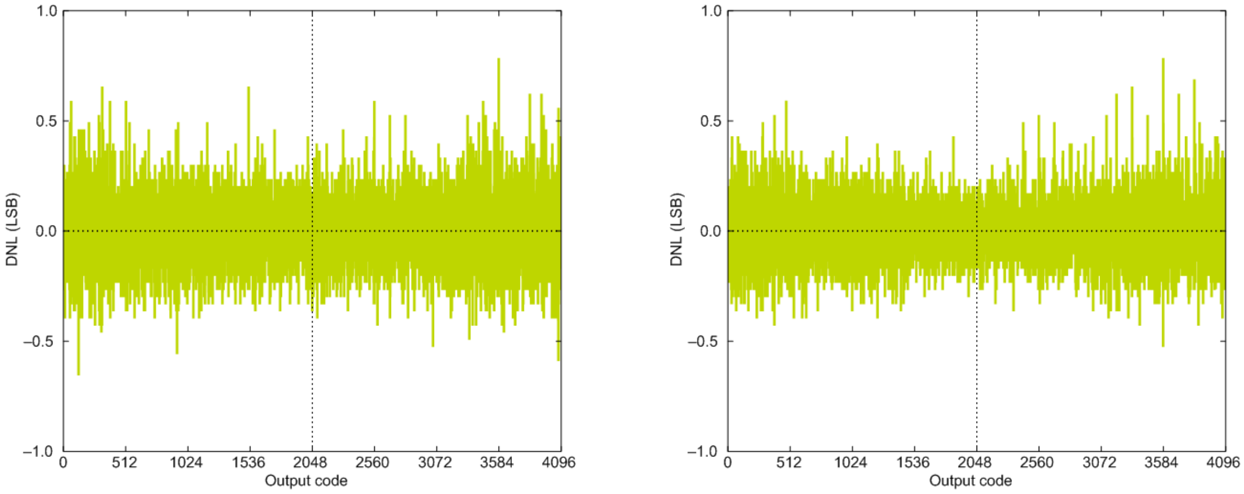
2XVDDVSS Reference

5VDIFF Reference



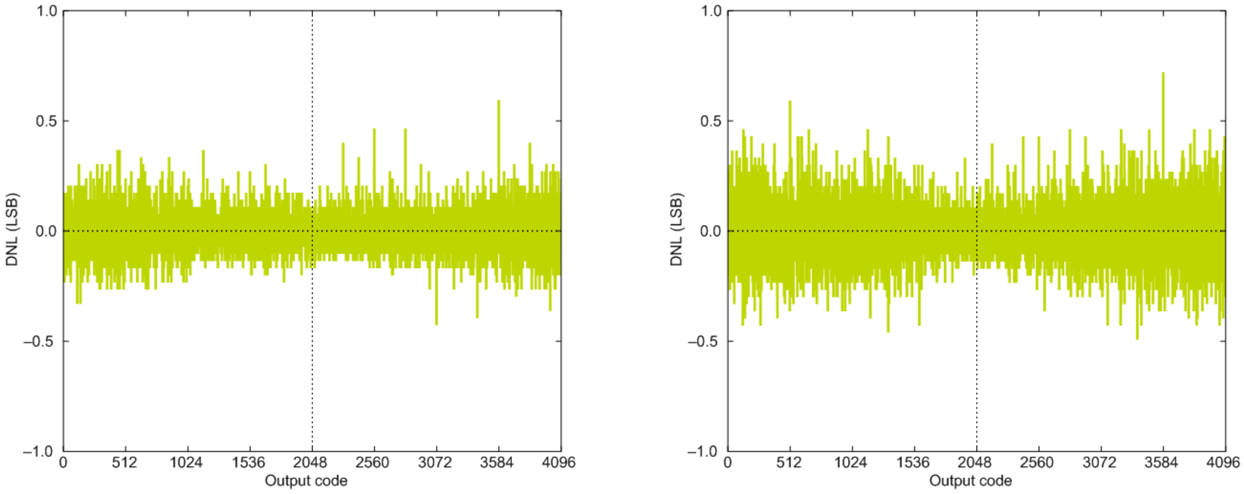
VDD Reference

Figure 3.31. ADC Differential Linearity Error vs Code, Vdd = 3V, Temp = 25°C



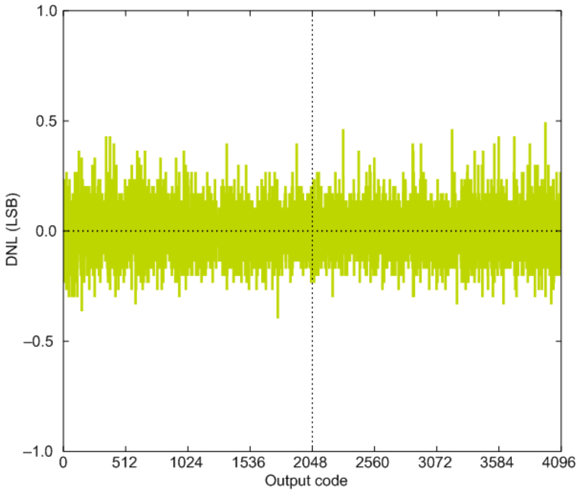
1.25V Reference

2.5V Reference



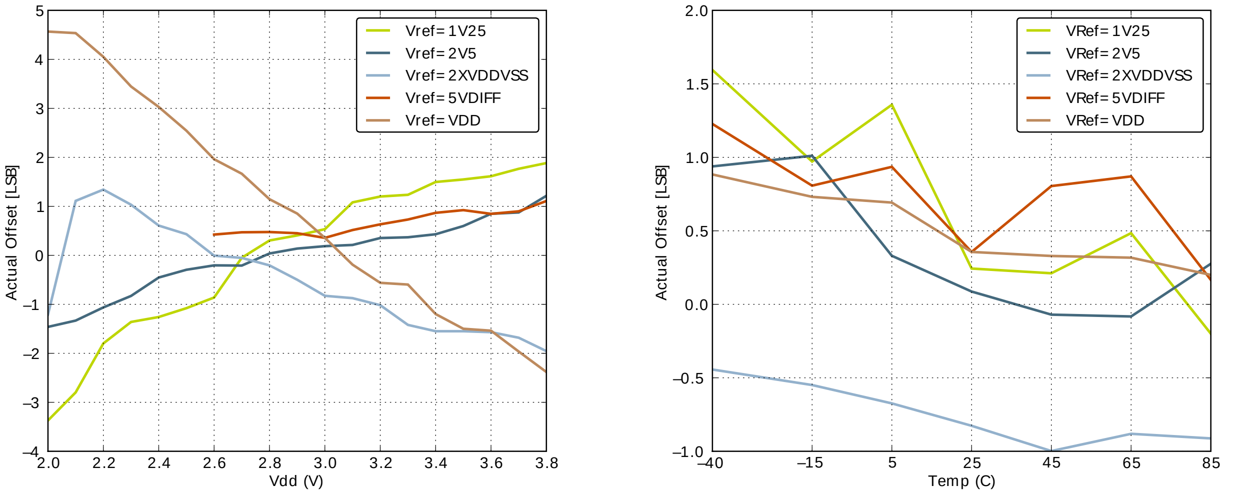
2XVDDVSS Reference

5VDIFF Reference



VDD Reference

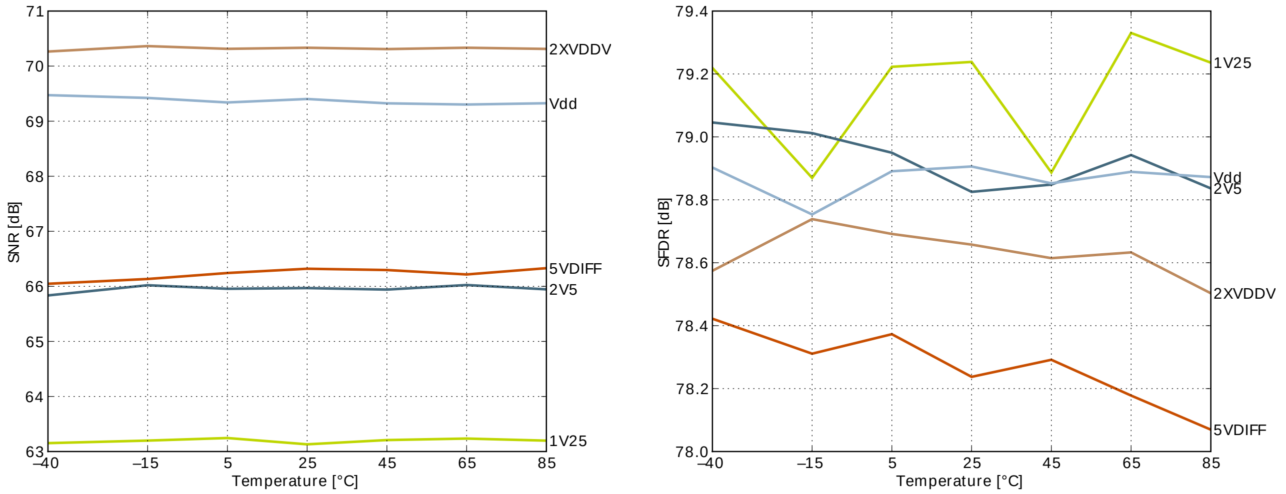
Figure 3.32. ADC Absolute Offset, Common Mode = Vdd /2



Offset vs Supply Voltage, Temp = 25°C

Offset vs Temperature, Vdd = 3V

Figure 3.33. ADC Dynamic Performance vs Temperature for all ADC References, Vdd = 3V



Signal to Noise Ratio (SNR)

Spurious-Free Dynamic Range (SFDR)

3.11 Digital Analog Converter (DAC)

Table 3.15. DAC

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{DACOUT}	Output voltage range	VDD voltage reference, single ended	0		V_{DD}	V
V_{DACCM}	Output common mode voltage range		0		V_{DD}	V
I_{DAC}	Active current including references for 2 channels	500 kSamples/s, 12bit		400[1]	650	µA
		100 kSamples/s, 12 bit		200[1]	250	µA
		1 kSamples/s 12 bit		17[1]	25	µA
SR_{DAC}	Sample rate				500	ksamples/s

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{DAC}	DAC clock frequency	Continuous Mode			1000	kHz
		Sample/Hold Mode			250	kHz
		Sample/Off Mode			250	kHz
$CYC_{DACCONV}$	Clock cyckles per conversion			2		
$t_{DACCONV}$	Conversion time		2			µs
$t_{DACSETTLE}$	Settling time			5		µs
SNR_{DAC}	Signal to Noise Ratio (SNR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		58		dB
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		59		dB
$SNDR_{DAC}$	Signal to Noise-pulse Distortion Ratio (SNDR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		57		dB
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		54		dB
$SFDR_{DAC}$	Spurious-Free Dynamic Range(SFDR)	500 kSamples/s, 12 bit, single ended, internal 1.25V reference		62		dBc
		500 kSamples/s, 12 bit, single ended, internal 2.5V reference		56		dBc
$V_{DACOFFSET}$	Offset voltage	After calibration, single ended		2		mV
$V_{DACSHMDRIFT}$	Sample-hold mode voltage drift			540		µV/ms
DNL_{DAC}	Differential non-linearity			±1		LSB
INL_{DAC}	Integral non-linearity			±5		LSB
MC_{DAC}	No missing codes			12		bits

---

[1] Measured with a static input code and no loading on the output.

3.12 Analog Comparator (ACMP)

Table 3.16. ACMP

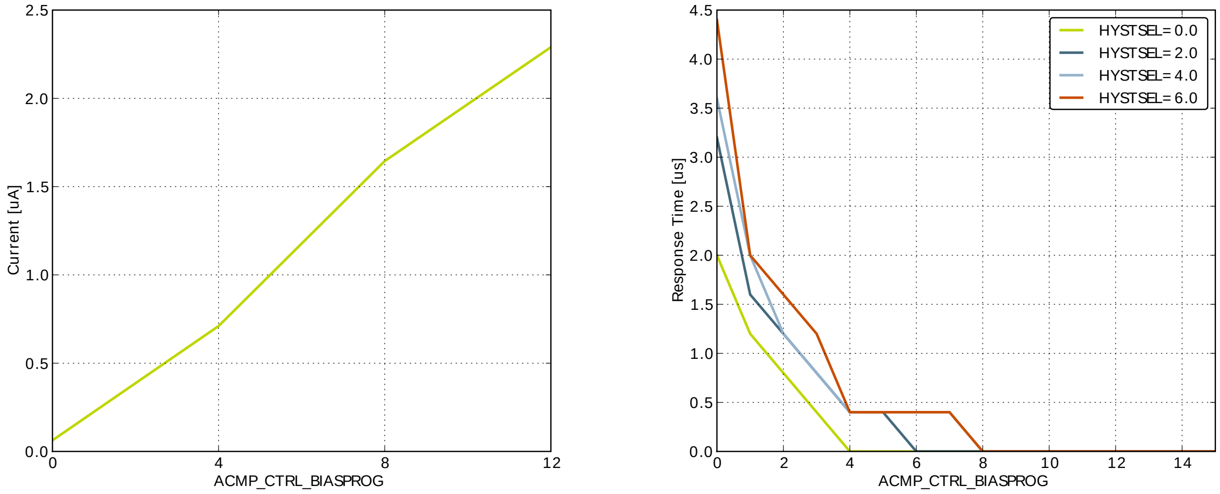
Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{ACMPIN}	Input voltage range		0		V_{DD}	V
V_{ACMPCM}	ACMP Common Mode voltage range		0		V_{DD}	V
I_{ACMP}	Active current	BIASPROG=0b0000, FULLBIAS=0 and HALFBIAS=1 in ACMPn_CTRL register		55	600	nA
		BIASPROG=0b1111, FULLBIAS=0 and HALFBIAS=0 in ACMPn_CTRL register		2.82	12	µA
		BIASPROG=0b1111, FULLBIAS=1 and HALFBIAS=0 in ACMPn_CTRL register		195	520	µA
$I_{ACMPREF}$	Current consumption of internal voltage reference	Internal voltage reference off. Using external voltage reference		0	0.5	µA
		Internal voltage reference, LPREF=1		0.050	3	µA
		Internal voltage reference, LPREF=0		6		µA
$V_{ACMPOFFSET}$	Offset voltage	BIASPROG= 0b1010, FULLBIAS=0 and HALFBIAS=0 in ACMPn_CTRL register	-12	0	12	mV
$V_{ACMPHYST}$	ACMP hysteresis	Programmable		17		mV
R_{CSRES}	Capacitive Sense Internal Resistance	CSRESSEL=0b00 in ACMPn_INPUTSEL		39		kOhm
		CSRESSEL=0b01 in ACMPn_INPUTSEL		71		kOhm
		CSRESSEL=0b10 in ACMPn_INPUTSEL		104		kOhm
		CSRESSEL=0b11 in ACMPn_INPUTSEL		136		kOhm
$t_{ACMPSTART}$	Startup time				10	µs

The total ACMP current is the sum of the contributions from the ACMP and its internal voltage reference as given in Equation 3.1 (p. 42) . $I_{ACMPREF}$ is zero if an external voltage reference is used.

Total ACMP Active Current

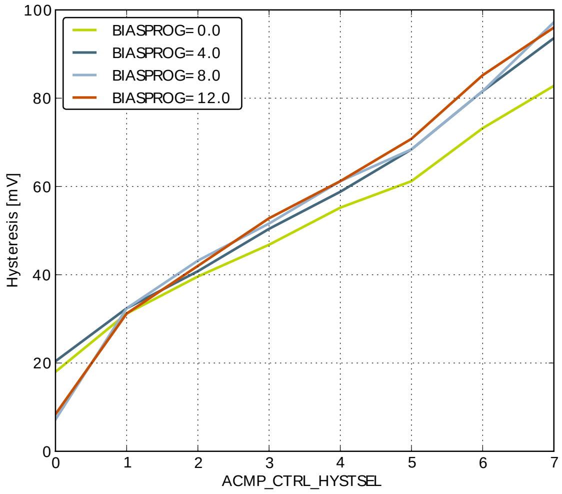
$$I_{ACMPTOTAL} = I_{ACMP} + I_{ACMPREF} \tag{3.1}$$

Figure 3.34. ACMP Characteristics, Vdd = 3V, Temp = 25°C, FULLBIAS = 0, HALFBIAS = 1



Current consumption, HYSTSEL = 4

Response time



Hysteresis

3.13 Voltage Comparator (VCMP)

Table 3.17. VCMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{VCMPIN}	Input voltage range			V_{DD}		V
V_{VCMPCM}	VCMP Common Mode voltage range			V_{DD}		V
I_{VCMP}	Active current	BIASPROG=0b0000 and HALFBIAS=1 in VCMPn_CTRL register		0.3	1	µA
		BIASPROG=0b1111 and HALFBIAS=0 in VCMPn_CTRL register. LPREF=0.		22	30	µA
$t_{VCMPREF}$	Startup time reference generator	NORMAL		10		µs
$V_{VCMPOFFSET}$	Offset voltage	Single ended		10		mV
		Differential		10		mV
$V_{VCMPHYST}$	VCMP hysteresis			17		mV
$t_{VCMPSTART}$	Startup time				10	µs

The V_{DD} trigger level can be configured by setting the TRIGLEVEL field of the VCMP_CTRL register in accordance with the following equation:

VCMP Trigger Level as a Function of Level Setting

$$V_{DD\ Trigger\ Level}=1.667V+0.034\times TRIGLEVEL \quad (3.2)$$

3.14 I2C

Table 3.18. I2C Standard-mode (Sm)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		100[1]	kHz
t_{LOW}	SCL clock low time	4.7			µs
t_{HIGH}	SCL clock high time	4.0			µs
$t_{SU,DAT}$	SDA set-up time	250			ns
$t_{HD,DAT}$	SDA hold time	8		3450[2,3]	ns
$t_{SU,STA}$	Repeated START condition set-up time	4.7			µs
$t_{HD,STA}$	(Repeated) START condition hold time	4.0			µs
$t_{SU,STO}$	STOP condition set-up time	4.0			µs
t_{BUF}	Bus free time between a STOP and START condition	4.7			µs

[1] For the minimum HFPERCLK frequency required in Standard-mode, see the I2C chapter in the EFM32G Reference Manual.

[2] The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).

[3] When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < ((3450*10^{-9} [s] * $f_{HFPERCLK}$ [Hz]) - 4).

Table 3.19. I2C Fast-mode (Fm)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		400[1]	kHz
t_{LOW}	SCL clock low time	1.3			µs
t_{HIGH}	SCL clock high time	0.6			µs
$t_{SU,DAT}$	SDA set-up time	100			ns
$t_{HD,DAT}$	SDA hold time	8		900[2,3]	ns
$t_{SU,STA}$	Repeated START condition set-up time	0.6			µs
$t_{HD,STA}$	(Repeated) START condition hold time	0.6			µs
$t_{SU,STO}$	STOP condition set-up time	0.6			µs
t_{BUF}	Bus free time between a STOP and START condition	1.3			µs

[1] For the minimum HFPERCLK frequency required in Fast-mode, see the I2C chapter in the EFM32G Reference Manual.
[2] The maximum SDA hold time ($t_{HD,DAT}$) needs to be met only when the device does not stretch the low time of SCL (t_{LOW}).
[3] When transmitting data, this number is guaranteed only when I2Cn_CLKDIV < ((900*10^{-9} [s] * $f_{HFPERCLK}$ [Hz]) - 4).

Table 3.20. I2C Fast-mode Plus (Fm+)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		1000[1]	kHz
t_{LOW}	SCL clock low time	0.5			µs
t_{HIGH}	SCL clock high time	0.26			µs
$t_{SU,DAT}$	SDA set-up time	50			ns
$t_{HD,DAT}$	SDA hold time	8			ns
$t_{SU,STA}$	Repeated START condition set-up time	0.26			µs
$t_{HD,STA}$	(Repeated) START condition hold time	0.26			µs
$t_{SU,STO}$	STOP condition set-up time	0.26			µs
t_{BUF}	Bus free time between a STOP and START condition	0.5			µs

[1] For the minimum HFPERCLK frequency required in Fast-mode Plus, see the I2C chapter in the EFM32G Reference Manual.

3.15 Digital Peripherals

Table 3.21. Digital Peripherals

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{USART}	USART current	USART idle current, clock enabled		7.5		µA/MHz
I_{UART}	UART current	UART idle current, clock enabled		5.63		µA/MHz
I_{LEUART}	LEUART current	LEUART idle current, clock enabled		150		nA
I_{I2C}	I2C current	I2C idle current, clock enabled		6.25		µA/MHz
I_{TIMER}	TIMER current	TIMER_0 idle current, clock enabled		8.75		µA/MHz
$I_{LETIMER}$	LETIMER current	LETIMER idle current, clock enabled		150		nA

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{PCNT}	PCNT current	PCNT idle current, clock enabled		100		nA
I_{RTC}	RTC current	RTC idle current, clock enabled		100		nA
I_{AES}	AES current	AES idle current, clock enabled		2.5		µA/MHz
I_{GPIO}	GPIO current	GPIO idle current, clock enabled		5.31		µA/MHz
I_{PRS}	PRS current	PRS idle current		2,81		µA/MHz
I_{DMA}	DMA current	Clock enable		8.12		µA/MHz

4 Pinout and Package

Note

Please refer to the application note "AN0002 EFM32 Hardware Design Considerations" for guidelines on designing Printed Circuit Boards (PCB's) for the EFM32G200.

4.1 Pinout

The *EFM32G200* pinout is shown in Figure 4.1 (p. 47) and Table 4.1 (p. 47). Alternate locations are denoted by "#" followed by the location number (Multiple locations on the same pin are split with "/"). Alternate locations can be configured in the LOCATION bitfield in the *_ROUTE register in the module in question.

Figure 4.1. EFM32G200 Pinout (top view, not to scale)

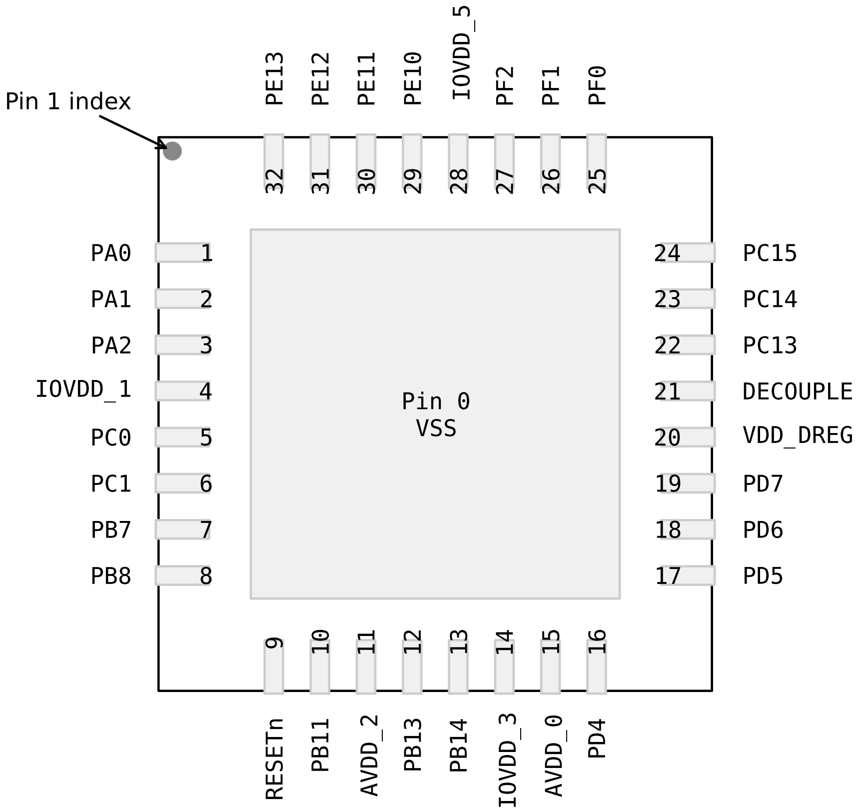


Table 4.1. Device Pinout

QFN32 Pin# and Name		Pin Alternate Functionality / Description			
Pin #	Pin Name	Analog	Timers	Communication	Other
0	VSS	Ground.			
1	PA0		TIM0_CC0 #0/1	I2C0_SDA #0	
2	PA1		TIM0_CC1 #0/1	I2C0_SCL #0	CMU_CLK1 #0

QFN32 Pin# and Name		Pin Alternate Functionality / Description			
Pin #	Pin Name	Analog	Timers	Communication	Other
3	PA2		TIM0_CC2 #0/1		CMU_CLK0 #0
4	IOVDD_1	Digital IO power supply 1.			
5	PC0	ACMP0_CH0	PCNT0_S0IN #2	US1_TX #0	
6	PC1	ACMP0_CH1	PCNT0_S1IN #2	US1_RX #0	
7	PB7	LFXTAL_P		US1_CLK #0	
8	PB8	LFXTAL_N		US1_CS #0	
9	RESETn	Reset input, active low. To apply an external reset source to this pin, it is required to only drive this pin low during reset, and let the internal pull-up ensure that reset is released.			
10	PB11	DAC0_OUT0	LETIM0_OUT0 #1		
11	AVDD_2	Analog power supply 2.			
12	PB13	HFXTAL_P		LEU0_TX #1	
13	PB14	HFXTAL_N		LEU0_RX #1	
14	IOVDD_3	Digital IO power supply 3.			
15	AVDD_0	Analog power supply 0.			
16	PD4	ADC0_CH4		LEU0_TX #0	
17	PD5	ADC0_CH5		LEU0_RX #0	
18	PD6	ADC0_CH6	LETIM0_OUT0 #0	I2C0_SDA #1	
19	PD7	ADC0_CH7	LETIM0_OUT1 #0	I2C0_SCL #1	
20	VDD_DREG	Power supply for on-chip voltage regulator.			
21	DECOUPLE	Decouple output for on-chip voltage regulator. An external capacitance of size $C_{DECOUPLE}$ is required at this pin.			
22	PC13	ACMP1_CH5	TIM0_CDTI0 #1/3 TIM1_CC0 #0 PCNT0_S0IN #0		
23	PC14	ACMP1_CH6	TIM0_CDTI1 #1/3 TIM1_CC1 #0 PCNT0_S1IN #0		
24	PC15	ACMP1_CH7	TIM0_CDTI2 #1/3 TIM1_CC2 #0		DBG_SWO #1
25	PF0		LETIM0_OUT0 #2		DBG_SWCLK #0/1
26	PF1		LETIM0_OUT1 #2		DBG_SWDIO #0/1
27	PF2				ACMP1_O #0 DBG_SWO #0
28	IOVDD_5	Digital IO power supply 5.			
29	PE10		TIM1_CC0 #1	US0_TX #0	BOOT_TX
30	PE11		TIM1_CC1 #1	US0_RX #0	BOOT_RX
31	PE12		TIM1_CC2 #1	US0_CLK #0	
32	PE13			US0_CS #0	ACMP0_O #0

4.2 Alternate Functionality Pinout

A wide selection of alternate functionality is available for multiplexing to various pins. This is shown in Table 4.2 (p. 49). The table shows the name of the alternate functionality in the first column, followed by columns showing the possible LOCATION bitfield settings.

Note

Some functionality, such as analog interfaces, do not have alternate settings or a LOCATION bitfield. In these cases, the pinout is shown in the column corresponding to LOCATION 0.

Table 4.2. Alternate functionality overview

Alternate	LOCATION				
Functionality	0	1	2	3	Description
ACMP0_CH0	PC0				Analog comparator ACMP0, channel 0.
ACMP0_CH1	PC1				Analog comparator ACMP0, channel 1.
ACMP0_O	PE13				Analog comparator ACMP0, digital output.
ACMP1_CH5	PC13				Analog comparator ACMP1, channel 5.
ACMP1_CH6	PC14				Analog comparator ACMP1, channel 6.
ACMP1_CH7	PC15				Analog comparator ACMP1, channel 7.
ACMP1_O	PF2				Analog comparator ACMP1, digital output.
ADC0_CH4	PD4				Analog to digital converter ADC0, input channel number 4.
ADC0_CH5	PD5				Analog to digital converter ADC0, input channel number 5.
ADC0_CH6	PD6				Analog to digital converter ADC0, input channel number 6.
ADC0_CH7	PD7				Analog to digital converter ADC0, input channel number 7.
BOOT_RX	PE11				Bootloader RX.
BOOT_TX	PE10				Bootloader TX.
CMU_CLK0	PA2				Clock Management Unit, clock output number 0.
CMU_CLK1	PA1				Clock Management Unit, clock output number 1.
DAC0_OUT0	PB11				Digital to Analog Converter DAC0 output channel number 0.
DBG_SWCLK	PF0	PF0			Debug-interface Serial Wire clock input. Note that this function is enabled to pin out of reset, and has a built-in pull down.
DBG_SWDIO	PF1	PF1			Debug-interface Serial Wire data input / output. Note that this function is enabled to pin out of reset, and has a built-in pull up.
DBG_SWO	PF2	PC15			Debug-interface Serial Wire viewer Output. Note that this function is not enabled after reset, and must be enabled by software to be used.
HFXTAL_N	PB14				High Frequency Crystal negative pin. Also used as external optional clock input pin.
HFXTAL_P	PB13				High Frequency Crystal positive pin.
I2C0_SCL	PA1	PD7			I2C0 Serial Clock Line input / output.
I2C0_SDA	PA0	PD6			I2C0 Serial Data input / output.
LETIM0_OUT0	PD6	PB11	PF0		Low Energy Timer LETIM0, output channel 0.
LETIM0_OUT1	PD7		PF1		Low Energy Timer LETIM0, output channel 1.
LEU0_RX	PD5	PB14			LEUART0 Receive input.
LEU0_TX	PD4	PB13			LEUART0 Transmit output. Also used as receive input in half duplex communication.
LFXTAL_N	PB8				Low Frequency Crystal (typically 32.768 kHz) negative pin. Also used as an optional external clock input pin.
LFXTAL_P	PB7				Low Frequency Crystal (typically 32.768 kHz) positive pin.
PCNT0_S0IN	PC13		PC0		Pulse Counter PCNT0 input number 0.
PCNT0_S1IN	PC14		PC1		Pulse Counter PCNT0 input number 1.

Alternate	LOCATION				
Functionality	**0**	**1**	**2**	**3**	**Description**
TIM0_CC0	PA0	PA0			Timer 0 Capture Compare input / output channel 0.
TIM0_CC1	PA1	PA1			Timer 0 Capture Compare input / output channel 1.
TIM0_CC2	PA2	PA2			Timer 0 Capture Compare input / output channel 2.
TIM0_CDTI0		PC13		PC13	Timer 0 Complimentary Deat Time Insertion channel 0.
TIM0_CDTI1		PC14		PC14	Timer 0 Complimentary Deat Time Insertion channel 1.
TIM0_CDTI2		PC15		PC15	Timer 0 Complimentary Deat Time Insertion channel 2.
TIM1_CC0	PC13	PE10			Timer 1 Capture Compare input / output channel 0.
TIM1_CC1	PC14	PE11			Timer 1 Capture Compare input / output channel 1.
TIM1_CC2	PC15	PE12			Timer 1 Capture Compare input / output channel 2.
US0_CLK	PE12				USART0 clock input / output.
US0_CS	PE13				USART0 chip select input / output.
US0_RX	PE11				USART0 Asynchronous Receive. USART0 Synchronous mode Master Input / Slave Output (MISO).
US0_TX	PE10				USART0 Asynchronous Transmit.Also used as receive input in half duplex communication. USART0 Synchronous mode Master Output / Slave Input (MOSI).
US1_CLK	PB7				USART1 clock input / output.
US1_CS	PB8				USART1 chip select input / output.
US1_RX	PC1				USART1 Asynchronous Receive. USART1 Synchronous mode Master Input / Slave Output (MISO).
US1_TX	PC0				USART1 Asynchronous Transmit.Also used as receive input in half duplex communication. USART1 Synchronous mode Master Output / Slave Input (MOSI).

4.3 GPIO Pinout Overview

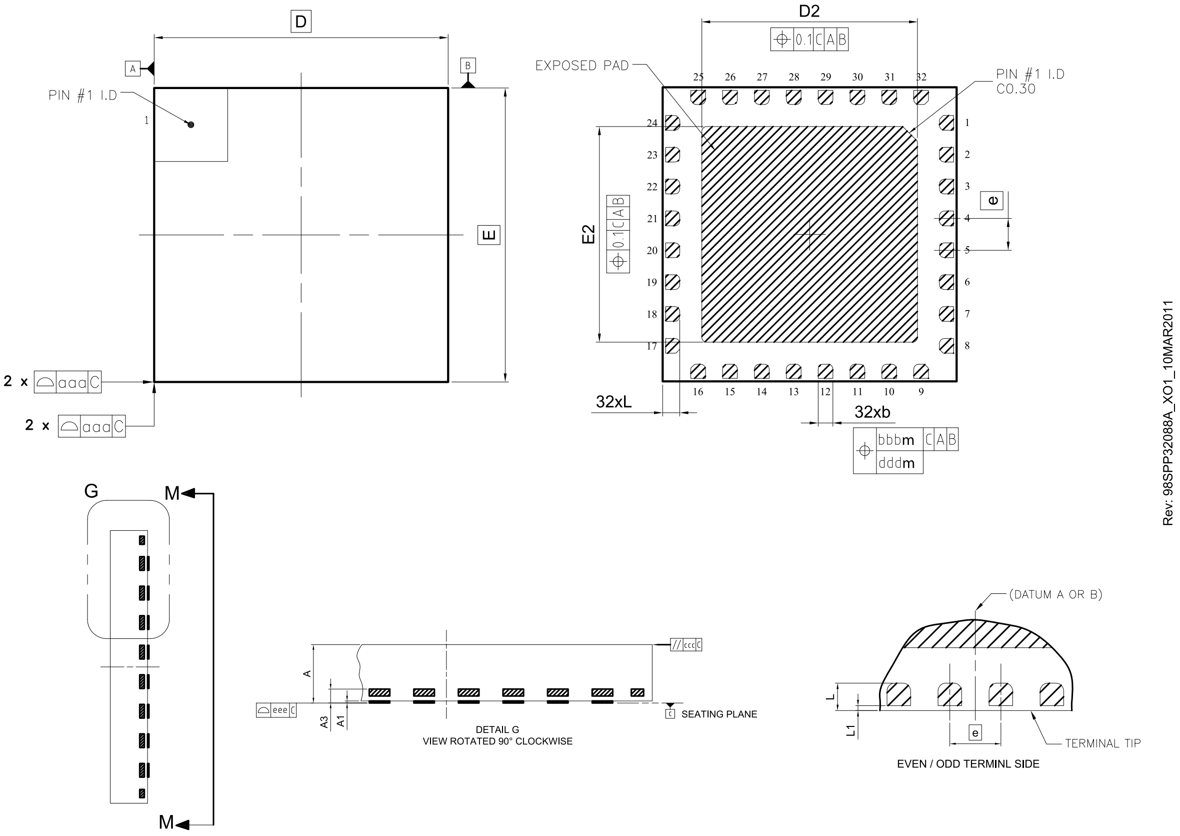
The specific GPIO pins available in *EFM32G200* is shown in Table 4.3 (p. 50). Each GPIO port is organized as 16-bit ports indicated by letters A through F, and the individual pin on this port is indicated by a number from 15 down to 0.

Table 4.3. GPIO Pinout

Port	Pin 15	Pin 14	Pin 13	Pin 12	Pin 11	Pin 10	Pin 9	Pin 8	Pin 7	Pin 6	Pin 5	Pin 4	Pin 3	Pin 2	Pin 1	Pin 0
Port A	-	-	-	-	-	-	-	-	-	-	-	-	-	PA2	PA1	PA0
Port B	-	PB14	PB13	-	PB11	-	-	PB8	PB7	-	-	-	-	-	-	-
Port C	PC15	PC14	PC13	-	-	-	-	-	-	-	-	-	-	-	PC1	PC0
Port D	-	-	-	-	-	-	-	-	PD7	PD6	PD5	PD4	-	-	-	-
Port E	-	-	PE13	PE12	PE11	PE10	-	-	-	-	-	-	-	-	-	-
Port F	-	-	-	-	-	-	-	-	-	-	-	-	-	PF2	PF1	PF0

4.4 QFN32 Package

Figure 4.2. QFN32



Note:

1. Dimensioning & tolerancing confirm to ASME Y14.5M-1994.
2. All dimensions are in millimeters. Angles are in degrees.
3. Dimension 'b' applies to metallized terminal and is measured between 0.25 mm and 0.30 mm from the terminal tip. Dimension L1 represents terminal full back from package edge up to 0.1 mm is acceptable.
4. Coplanarity applies to the exposed heat slug as well as the terminal.
5. Radius on terminal is optional

Table 4.4. QFN32 (Dimensions in mm)

Symbol	A	A1	A3	b	D	E	D2	E2	e	L	L1	aaa	bbb	ccc	ddd	eee
Min	0.80	0.00	0.203 REF	0.25	6.00 BSC	6.00 BSC	4.30	4.30	0.65 BSC	0.30	0.00	0.10	0.10	0.10	0.05	0.08
Nom	0.85	-		0.30			4.40	4.40		0.35						
Max	0.90	0.05		0.35			4.50	4.50		0.40	0.10					

The QFN32 package uses Nickel-Palladium-Gold preplated leadframe.

All EFM32 packages are RoHS compliant and free of Bromine (Br) and Antimony (Sb).

For additional Quality and Environmental information, please see:
http://www.silabs.com/support/quality/pages/default.aspx

5 PCB Layout and Soldering

5.1 Recommended PCB Layout

Figure 5.1. QFN32 PCB Land Pattern

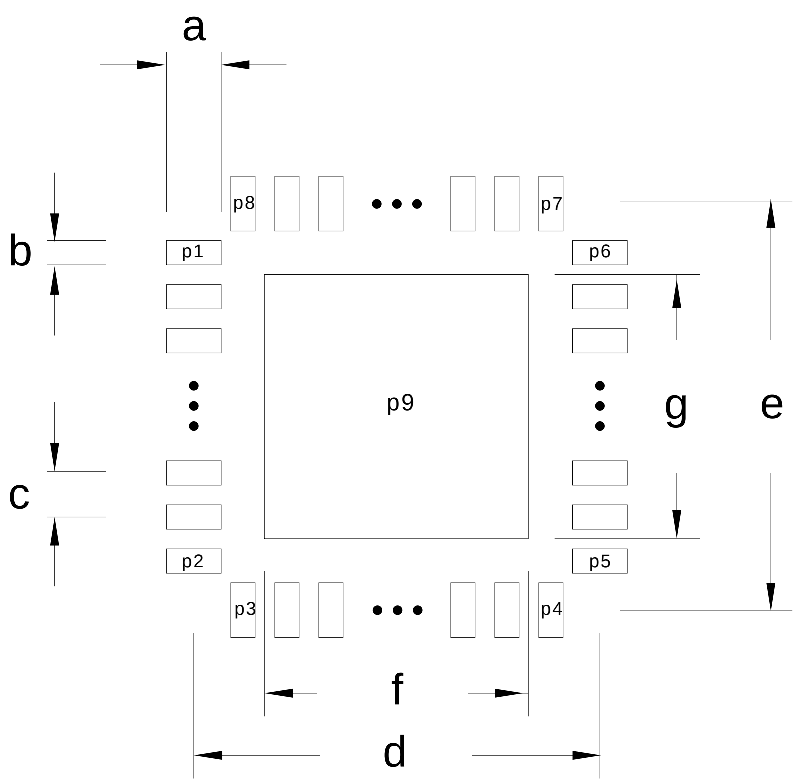


Table 5.1. QFN32 PCB Land Pattern Dimensions (Dimensions in mm)

Symbol	Dim. (mm)	Symbol	Pin number	Symbol	Pin number
a	0.80	P1	1	P6	24
b	0.35	P2	8	P7	25
c	0.65	P3	26	P8	32
d	6.00	P4	16	P9	33
e	6.00	P5	17	-	-
f	4.40	-	-	-	-
g	4.40	-	-	-	-

Figure 5.2. QFN32 PCB Solder Mask

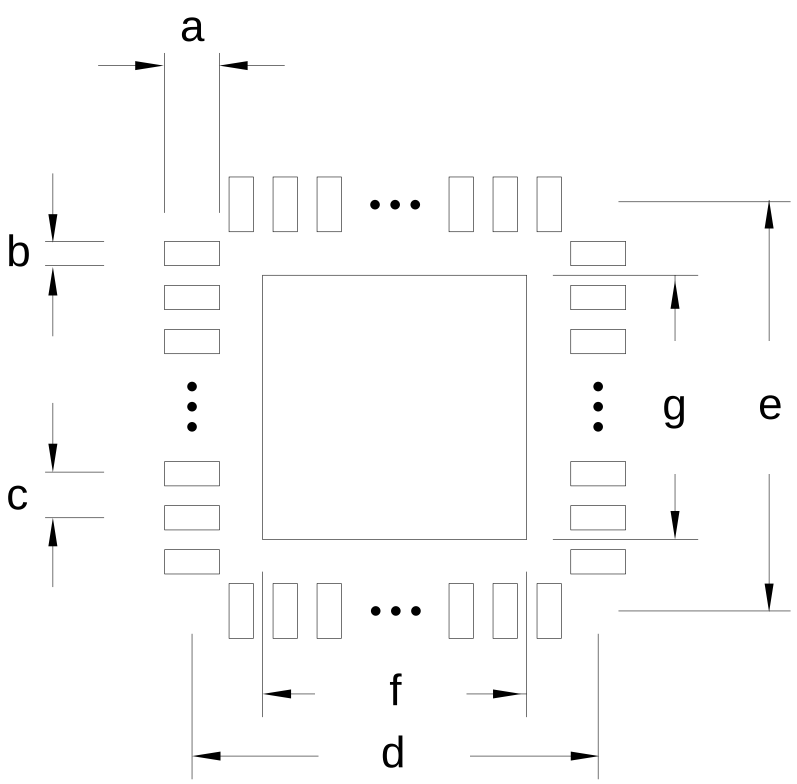


Table 5.2. QFN32 PCB Solder Mask Dimensions (Dimensions in mm)

Symbol	Dim. (mm)
a	0.92
b	0.47
c	0.65
d	6.00
e	6.00
f	4.52
g	4.52

Figure 5.3. QFN32 PCB Stencil Design

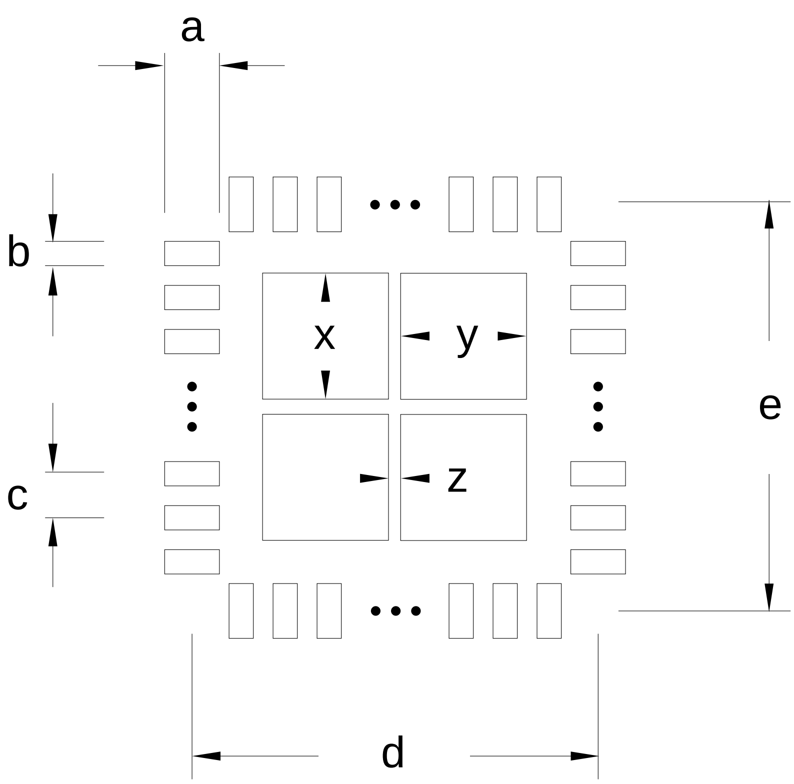


Table 5.3. QFN32 PCB Stencil Design Dimensions (Dimensions in mm)

Symbol	Dim. (mm)
a	0.70
b	0.25
c	0.65
d	6.00
e	6.00
x	1.30
y	1.30
z	0.50

1. The drawings are not to scale.
2. All dimensions are in millimeters.
3. All drawings are subject to change without notice.
4. The PCB Land Pattern drawing is in compliance with IPC-7351B.
5. Stencil thickness 0.125 mm.
6. For detailed pin-positioning, see Figure 4.2 (p. 51) .

5.2 Soldering Information

The latest IPC/JEDEC J-STD-020 recommendations for Pb-Free reflow soldering should be followed.

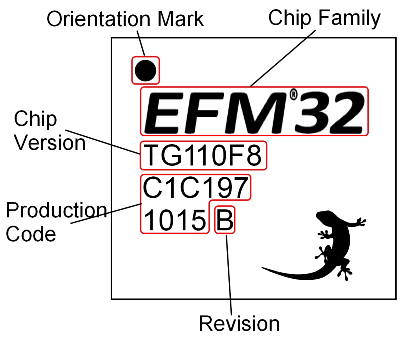
Place as many and as small as possible vias underneath each of the solder patches under the ground pad.

6 Chip Marking, Revision and Errata

6.1 Chip Marking

In the illustration below package fields and position are shown.

Figure 6.1. Example Chip Marking (top view)



6.2 Revision

The revision of a chip can be determined from the "Revision" field in Figure 6.1 (p. 55) .

6.3 Errata

Please see the errata document for EFM32G200 for description and resolution of device erratas. This document is available in Simplicity Studio and online at:
http://www.silabs.com/support/pages/document-library.aspx?p=MCUs--32-bit

7 Revision History

7.1 Revision 1.90

May 22nd, 2015

Added clarification on conditions for INL_{ADC} and DNL_{ADC} parameters.

Corrected EM2 current consumption condition in Electrical Characteristics section.

Added AUXHFRCO to block diagram and Electrical Characteristics.

Updated HFRCO table in the Electrical Characteristics section.

Updated EM0, EM2, EM3, and EM4 maximum current specifications in the Electrical Characteristics section.

Updated the Output Low Voltage maximum for sinking 20 mA with VDD = 3.0 V in the Electrical Characteristics section.

Updated the Input Leakage Current maximum in the Electrical Characteristics section.

Updated the minimum and maximum frequency specifications for the LFRCO, HFRCO, and AUXHFRCO in the Electrical Characteristics section.

Updated the maximum current consumption of the HFRCO in the Electrical Characteristics section.

Updated the maximum current consumption of the HFRCO in the Electrical Characteristics section.

Added some minimum ADC SNR, SNDR, and SFDR specifications in the Electrical Characteristics section.

Added some minimum and maximum ADC offset voltage, DNL, and INL specifications in the Electrical Characteristics section.

Added maximum DAC current specifications in the Electrical Characteristics section.

Added maximum ACMP current and maximum and minimum offset voltage specifications in the Electrical Characteristics section.

Added maximum VCMP current and updated typical VCMP current specifications in the Electrical Characteristics section.

Updated references to energyAware Designer to Configurator.

7.2 Revision 1.80

July 2nd, 2014

Corrected single power supply voltage minimum value from 1.85V to 1.98V.

Updated current consumption.

Updated transition between energy modes.

Updated power management data.

Updated GPIO data.

Updated LFXO, HFXO, HFRCO and ULFRCO data.

Updated LFRCO and HFRCO plots.

Updated ACMP data.

7.3 Revision 1.71

November 21st, 2013

Updated figures.

Updated errata-link.

Updated chip marking.

Added link to Environmental and Quality information.

Re-added missing DAC-data.

7.4 Revision 1.70

September 30th, 2013

Added I2C characterization data.

Corrected GPIO operating voltage from 1.8 V to 1.85 V.

Corrected the ADC resolution from 12, 10 and 6 bit to 12, 8 and 6 bit.

Updated Environmental information.

Updated trademark, disclaimer and contact information.

Other minor corrections.

7.5 Revision 1.60

June 28th, 2013

Updated power requirements in the Power Management section.

Removed minimum load capacitance figure and table. Added reference to application note.

Other minor corrections.

7.6 Revision 1.50

September 11th, 2012

Updated the HFRCO 1 MHz band typical value to 1.2 MHz.

Updated the HFRCO 7 MHz band typical value to 6.6 MHz.

Other minor corrections.

7.7 Revision 1.40

February 27th, 2012

Updated Power Management section.

Corrected operating voltage from 1.8 V to 1.85 V.

Corrected $\mathrm{TGRAD}_{\mathrm{ADCTH}}$ parameter.

Corrected QFN32 package drawing.

Updated PCB land pattern, solder mask and stencil design.

7.8 Revision 1.30

May 20th, 2011

Updated LFXO load capacitance section.

7.9 Revision 1.20

December 17th, 2010

Increased max storage temperature.

Added data for <150°C and <70°C on Flash data retention.

Changed latch-up sensitivity test description.

Added IO leakage current.

Added Flash current consumption.

Updated HFRCO data.

Updated LFRCO data.

Added graph for ADC Absolute Offset over temperature.

Added graph for ADC Temperature sensor readout.

7.10 Revision 1.11

November 17th, 2010

Corrected maximum DAC clock speed for continuous mode.

Added DAC sample-hold mode voltage drift rate.

Added pulse widths detected by the HFXO glitch detector.

Added power sequencing information to Power Management section.

7.11 Revision 1.10

September 13th, 2010

Added typical values for $\mathrm{R}_{\mathrm{ADCFILT}}$ and $\mathrm{C}_{\mathrm{ADCFILT}}$.

Added two conditions for DAC clock frequency; one for sample/hold and one for sample/off.

Added RoHS information and specified leadframe/solderballs material.

Added Serial Bootloader to feature list and system summary.

Updated ADC characterization data.

Updated DAC characterization data.

Updated RCO characterization data.

Updated ACMP characterization data.

Updated VCMP characterization data.

7.12 Revision 1.00

April 23rd, 2010

ADC_VCM line removed.

Added pinout illustration and additional pinout table.

Changed "Errata" chapter. Errata description moved to separate document.

Document changed status from "Preliminary".

Updated "Electrical Characteristics" chapter.

7.13 Revision 0.85

February 19th, 2010

Renamed DBG_SWV pin to DBG_SWO.

7.14 Revision 0.83

January 25th, 2010

Updated errata section.

Specified flash word width in Section 3.7 (p. 17) .

Added Capacitive Sense Internal Resistor values in Section 3.12 (p. 42) .

7.15 Revision 0.82

December 9th, 2009

Updated contact information.

ADC current consumption numbers updated in Section 3.10 (p. 31) .

7.16 Revision 0.81

November 20th, 2009

Section 2.1.21 (p. 6) updated.

Section 3.1 (p. 8) updated.

Storage temperature in Section 3.2 (p. 8) updated.

Temperature coefficient of band-gap reference in Section 3.6 (p. 16) added.

Erase times in Section 3.7 (p. 17) updated.

Definitions of DNL and INL added in Figure 3.27 (p. 35) and Figure 3.28 (p. 36) .

Current consumption of digital peripherals added in Section 3.15 (p. 45) .

Updated errata section.

7.17 Revision 0.80

Initial preliminary revision, October 19th, 2009

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